KE1xZP100M96SF0 Kinetis KE17Z/13Z/12Z with up to 512 KB Flash

Rev. 2 - 04/2024

Data Sheet: Technical Data

- This document provides electrical specifications for Kinetis KE17Z/13Z/12Z with up to 512 KB Flash Data Sheet
- For functional characteristics and the programming model, see Kinetis KE17Z/13Z/12Z with up to 512 KB Flash Reference Manual.



NXP reserves the right to change the detail specifications as may be required to permit improvements in the design of its products.

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1 Kinetis KE17Z/13Z/12Z introduction

Kinetis KE17Z/13Z/12Z with up to 512 KB Flash

Up to 96 MHz ARM[®] Cortex[®]-M0+ Based Microcontroller

KE1xZ512 MCUs are the leading parts for the KE1xZ family based on ARM[®] Cortex[®]-M0+ core. Providing up to 512 KB flash, up to 96 KB RAM, and the enhanced dual Touch Sensing Interface (TSI) module extends Kinetis E family to 50 touch channels. Enhanced robust TSI provides high level stability and accuracy to help customer develop HMI system easily and quickly. 1 Msps ADC and FlexTimer help build a perfect solution for BLDC motor control systems.

Core Processor and System

- ARM[®] Cortex[®]-M0+ core, supports up to 96 MHz frequency
- ARM Core based on the ARMv6 Architecture and Thumb[®]-2 ISA
- Configurable Nested Vectored Interrupt Controller (NVIC)
- 8-channel DMA controller extended up to 63 channels with DMAMUX

Reliability, safety, and security

- Cyclic Redundancy Check (CRC) generator module
- 128-bit unique identification (ID) number
- · Internal watchdog (WDOG) with independent clock source
- · External watchdog monitor (EWM) module
- · ADC self-calibration feature
- On-chip clock loss monitoring

Human-machine interface (HMI)

- · Supports up to 32 interrupt request (IRQ) sources
- · Up to 89 GPIO pins with interrupt functionality
- 2x Touch sensing input (TSI) modules, each TSI has up to 25 channels

Memory and memory interfaces

- Up to 512 KB program flash, dual-bank flash supporting flash SWAP feature
- Up to 96 KB SRAM
- 256 Bytes flash cache

Mixed-signal analog

- 1× 12-bit analog-to-digital converter (ADC) with up to 24 channel analog inputs per module, up to 1 Msps
- 1× high-speed analog comparator (CMP) with internal 8-bit digital to analog converter (DAC)

Timing and control

- 3× Flex Timers (FTM) for PWM generation, offering up to 16 standard channels
- 1× 16-bit Low-Power Timer (LPTMR) with flexible wake up control
- 1× 32-bit Low-power Periodic Interrupt Timer (LPIT) with 4 channels
- 1x Real Time Clock (RTC)

Clock interfaces

- OSC: high range 4 40 MHz (with high-gain mode) and low range 32 40 kHz (with low-gain mode)
- 48 60 MHz high-accuracy (up to ±1%) fast internal reference clock (FIRC) for normal Run

- 8 MHz / 2 MHz high-accuracy (up to ±3%) slow internal reference clock (SIRC) for low-speed Run
- 128 kHz low power oscillator (LPO)
- Low-power FLL (LPFLL)
- · Up to 60 MHz DC external square wave input clock
- System clock generator (SCG)

Power management

- Low-power ARM Cortex-M0+ core with excellent energy efficiency
- Power management controller (PMC) with multiple power modes: HSRUN, Run, Wait, Stop, VLPR, VLPW, and VLPS
- · Supports clock gating for unused modules, and specific peripherals remain working in low power modes
- · POR, LVD, and LVR

Connectivity and communications interfaces

- 3× low-power universal asynchronous receiver / transmitter (LPUART) modules with DMA support and low power availability
- · 2x Serial Communications Interface (SCI) modules with DMA support and LIN slave operation
- · 2× low-power serial peripheral interface (LPSPI) modules with DMA support and low power availability
- · 2× low-power inter-integrated circuit (LPI2C) modules with DMA support and low power availability
- · FlexIO module for flexible and high performance serial interfaces

Debug functionality

- Serial Wire Debug (SWD) debug interface
- Debug Watchpoint and Trace (DWT)
- Micro Trace Buffer (MTB)

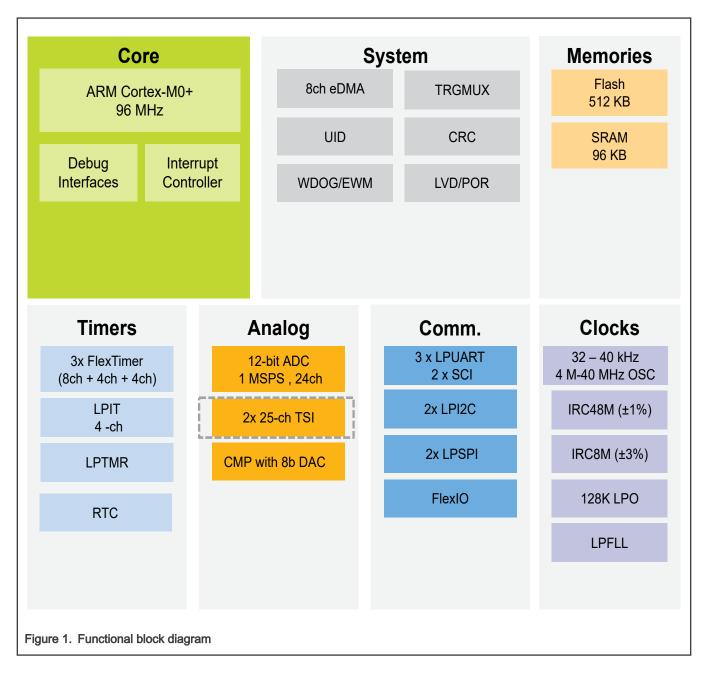
Operating Characteristics

- Voltage range: 2.7 to 5.5 V
- Ambient temperature range: -40 to 105 °C

Table 1. Related Resources

Туре	Description	Resource
Fact Sheet	The Fact Sheet gives overview of the product key features and its uses.	KE1xZ Family Fact Sheet KE1xZMCUFAMFS
Reference Manual	The Reference Manual contains a comprehensive description of the structure and function (operation) of a device.	KE1xZP100M96SF0RM ¹
Data Sheet	The Data Sheet includes electrical characteristics and signal connections.	This document: KE1xZP100M96SF0 ¹
Chip Errata	The chip mask set Errata provides additional or corrective information for a particular device mask set.	Kinetis_E_P83J ¹
Package drawing	Package dimensions are provided in package drawings.	100-LQFP: 98ASS23308W 64-LQFP: 98ASS23234W

1. To find the associated resource, go to http://www.nxp.com and perform a search using this term.



1.1 Ordering information

The following chips are available for ordering.

Table 2. Ordering information

Part number	Frequency	Flash	SRAM	TSI	GPIOs (INT/ HD) ¹	ADC	Package
MKE17Z512VLL9	96 MHz	512 KB	96 KB	50-Channel (TSI0, TSI1)	89/8	24-Channel	100 LQFP
MKE17Z512VLH9	96 MHz	512 KB	96 KB	47-Channel (TSI0, TSI1)	58/8	24-Channel	64 LQFP

Table continues on the next page...

Table 2. Ordering information (continued)

Part number	Frequency	Flash	SRAM	TSI	GPIOs (INT/ HD) ¹	ADC	Package
MKE13Z512VLL9	96 MHz	512 KB	96 KB	25-Channel (TSI0)	89/8	24-Channel	100 LQFP
MKE13Z512VLH9	96 MHz	512 KB	96 KB	22-Channel (TSI0)	58/8	24-Channel	64 LQFP
MKE12Z512VLL9	96 MHz	512 KB	96 KB	_	89/8	24-Channel	100 LQFP
MKE12Z512VLH9	96 MHz	512 KB	96 KB	_	58/8	24-Channel	64 LQFP

1. INT: interrupt pin numbers; HD: high drive pin numbers

1.2 Part identification

1.2.1 Description

Part numbers for the chip have fields that identify the specific part. You can use the values of these fields to determine the specific part you have received.

1.2.2 Format

Part numbers for this device have the following format: Q KE## A FFF R T PP CC N

1.2.3 Fields

This table lists the possible values for each field in the part number (not all combinations are valid):

Table 3. Part number fields description

Field	Description	Values
Q	Qualification status	M = Fully qualified, general market flow
		 P = Prequalification
KE##	Kinetis family	• KE17, KE13, KE12
A	Key attribute	• Z = Cortex-M0+
FFF	Program flash memory size	• 128 = 128 KB
		• 256 = 256 KB
		• 512 = 512 KB
R	Silicon revision	• (Blank) = Main
		 A = Revision after main
т	Temperature range (°C)	• V = -40 to 105
PP	Package identifier	• LH = 64 LQFP (10 mm x 10 mm)
		• LL = 100 LQFP (14 mm x 14 mm)

Table continues on the next page ...

СС	Maximum CPU frequency (MHz)	• 9 = 96 MHz
N	Packaging type	• R = Tape and reel
		 (Blank) = Trays

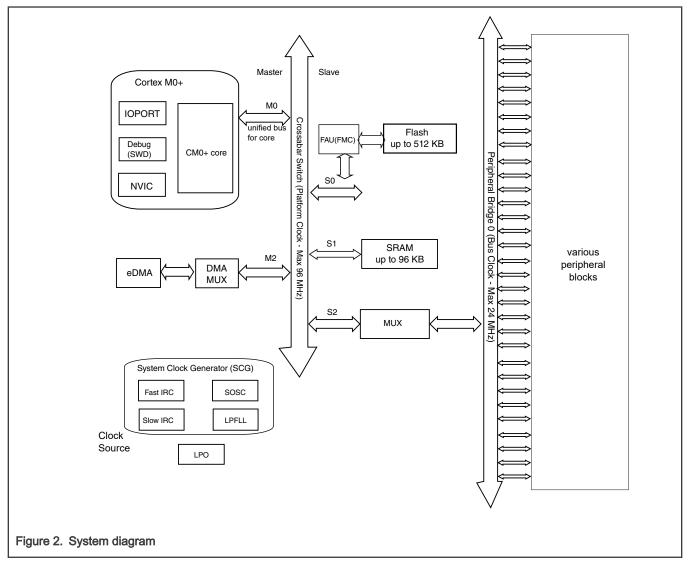
Table 3. Part number fields description (continued)

1.2.4 Example

This is an example part number: MKE17Z512VLL9

2 Overview

The following figure shows the system diagram of this device.



The crossbar switch connects bus masters and slaves using a crossbar switch structure. This structure allows up to four bus masters to access different bus slaves simultaneously, while providing arbitration among the bus masters when they access the same slave.

2.1 System features

The following sections describe the high-level system features.

2.1.1 ARM Cortex-M0+ core

The enhanced ARM Cortex M0+ is the member of the Cortex-M Series of processors targeting microcontroller cores focused on very cost sensitive, low power applications. It has a single 32-bit AMBA AHB-Lite interface and includes an NVIC component. It also has hardware debug functionality including support for simple program trace capability. The processor supports the ARMv6-M instruction set (Thumb) architecture including all but three 16-bit Thumb opcodes (52 total) plus seven 32-bit instructions. It is upward compatible with other Cortex-M profile processors.

2.1.2 NVIC

The Nested Vectored Interrupt Controller supports nested interrupts and 4 priority levels for interrupts. In the NVIC, each source in the IPR registers contains 2 bits. It also differs in number of interrupt sources and supports 32 interrupt vectors.

The Cortex-M family uses a number of methods to improve interrupt latency to up to 15 clock cycles for Cortex-M0+. It also can be used to wake the MCU core from Wait and VLPW modes.

2.1.3 AWIC

The asynchronous wake-up interrupt controller (AWIC) is used to detect asynchronous wake-up events in Stop mode and signal to clock control logic to resume system clocking. After clock restarts, the NVIC observes the pending interrupt and performs the normal interrupt or event processing. The AWIC can be used to wake MCU core from Partial Stop, Stop and VLPS modes.

Wake-up sources for this SoC are listed as below:

Wake-up source	Description
Available system resets	RESET pin, WDOG
Pin interrupts	Port Control Module - Any enabled pin interrupt is capable of waking the system
ADC0	ADC0 is optional functional with clock source from SIRC or OSC
CMP0	Functional in Stop/VLPS modes with clock source from SIRC or OSC
LPI2C	Functional in Stop/VLPS modes with clock source from SIRC or OSC
LPUART	Functional in Stop/VLPS modes with clock source from SIRC or OSC
LPSPI	Functional in Stop/VLPS modes with clock source from SIRC or OSC
LPTMR	Functional in Stop/VLPS modes
RTC	Functional in Stop/VLPS modes
TSI	Touch sense wakeup
NMI	Non-maskable interrupt

Table 4.	AWIC Stop	and VLPS	Wake-up	Sources
rabio r.	7.0000000		Traite up	0001000

2.1.4 Memory

This device has the following features:

- Up to 512 KB of embedded program flash memory, dual-bank flash supporting flash SWAP feature.
- Up to 96 KB of embedded RAM accessible (read/write) at CPU clock speed with 0 wait states.

2.1.5 Reset and boot

The following table lists all the reset sources supported by this device.

NOTE In the following table, Y means the specific module, except for the registers, bits or conditions mentioned in the footnote, is reset by the corresponding Reset source. N means the specific module is not reset by the corresponding Reset source.

Table 5. Reset source

Reset	Descriptions					Ν	lodules				
sources		PMC	SIM	SMC	RCM	Reset pin is negated	WDOG	SCG	LPTMR	RTC	Others
POR reset	Power-on reset (POR)	Y	Y	Y	Y	Y	Y	Y	Y	Y	Y
System resets	Low-voltage detect (LVD)	Y ¹ , ²	Y	Y	Y	Y	Y	Y	Y	Y	Y
	External pin reset (RESET)	Y ¹	Y	Y	Y	Y	Y	Y	N	N	Y
	Watchdog (WDOG) reset	Y ¹	Y ³	Y ⁴	Y ⁵	Y	Y ⁶	Y ⁷	N	N	Y
	Multipurpose clock generator loss of clock (LOC) reset	Y ¹	Y ³	Y ⁴	Y ⁵	Y	Y ⁶	Y ⁷	N	N	Y
	Multipurpose clock generator loss of lock (LOL) reset	Y ¹	Y ³	Y ⁴	Y ⁵	Y	Y ⁶	Y ⁷	N	N	Y
	Stop mode acknowledge error (SACKERR)	Y ¹	Y ³	Y ⁴	Y ⁵	Y	Y ⁶	Y ⁷	N	N	Y
	Software reset (SW)	Y ¹	Y ³	Y ⁴	Y ⁵	Y	Y ⁶	Y7	N	N	Y
	Lockup reset (LOCKUP)	Y ¹	Y ³	Y ⁴	Y ⁵	Y	Y ⁶	Y ⁷	N	N	Y
	MDM DAP system reset	Y ¹	Y ³	Y ⁴	Y ⁵	Y	Y ⁶	Y ⁷	N	N	Y
Debug reset	Debug reset	Y ¹	Y ³	Y ⁴	Y ⁵	Y	Y ⁶	Y7	N	N	Y

1. Except PMC_LVDSC1[LVDRE]

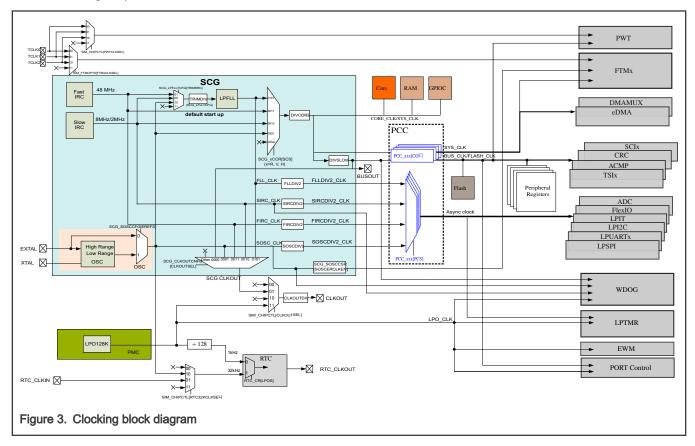
2. Except PMC_REGSC[LPODIS]

- 3. Except LPOTRIM[LPOTRIM]
- 4. Except SMC_PMPROT, SMC_PMCTRL_RUNM, SMC_PMCTRL_STOPM, SMC_STOPCTRL, SMC_PMSTAT
- 5. Except RCM_RPC, RCM_SRIE, RCM_SRS, RCM_SSRS
- 6. Except WDOG_CS[TST]
- 7. Except SCG_CSR and SCG_FIRCSTAT

2.1.6 Clock options

The SCG module controls which clock source is used to derive the system clocks. The clock generation logic divides the selected clock source into a variety of clock domains, including the clocks for the system bus masters, system bus slaves, and flash memory. The clock generation logic also implements module-specific clock gating to allow granular shutoff of modules.

The following figure is a high level block diagram of the clock generation. For more details on the clock operation and configuration, see the Clocking chapter in the Reference Manual.



2.1.7 Security

Security state can be enabled via programming flash configure field (0x40c). After enabling device security, the SWD port cannot access the memory resources of the MCU.

Table 6. Security state

External interface	Security	Unsecure
SWD port	Cannot access memory source by SWD interface	The debugger can write to the Flash Mass Erase in Progress field of the MDM- AP Control register to trigger a mass erase (Erase All Blocks) command.

2.1.8 Power management

The Power Management Controller (PMC) expands upon ARM's operational modes of Run, Sleep, and Deep Sleep, to provide multiple configurable modes. These modes can be used to optimize current consumption for a wide range of applications. The WFI or WFE instruction invokes a Wait or a Stop mode, depending on the current configuration. For more information on ARM's operational modes, See the ARM[®] Cortex[®] User Guide.

The PMC provides High Speed Run (HSRUN), Normal Run (RUN), and Very Low Power Run (VLPR) configurations in ARM's Run operation mode. In these modes, the MCU core is active and can access all peripherals. The difference between the modes is the maximum clock frequency of the system and therefore the power consumption. The configuration that matches the power versus performance requirements of the application can be selected.

The PMC provides Wait (Wait) and Very Low Power Wait (VLPW) configurations in ARM's Sleep operation mode. In these modes, even though the MCU core is inactive, all of the peripherals can be enabled and operate as programmed. The difference between the modes is the maximum clock frequency of the system and therefore the power consumption.

The PMC provides Stop (Stop), Very Low Power Stop (VLPS) configurations in ARM's Deep Sleep operational mode. In these modes, the MCU core and most of the peripherals are disabled. Depending on the requirements of the application, different portions of the analog, logic, and memory can be retained or disabled to conserve power.

The Nested Vectored Interrupt Controller (NVIC), the Asynchronous Wake-up Interrupt Controller (AWIC) are used to wake up the MCU from low power states. The NVIC is used to wake up the MCU core from WAIT and VLPW modes. The AWIC is used to wake up the MCU core from STOP and VLPS modes.

For additional information regarding operational modes, power management, the NVIC, AWIC, please see the Reference Manual.

The following table provides information about the state of the peripherals in the various operational modes and the modules that can wake MCU from low power modes.

Core mode	Device mode	Descriptions				
Run mode	High Speed Run (HSRUN)In HSRUN mode, the MCU is able to operate at a faster frequency of normal run mode.					
	Run	In Run mode, all device modules are operational.				
	Very Low Power Run	In VLPR mode, all device modules are operational at a reduced frequency except the Low Voltage Detect (LVD) monitor, which is disabled.				
Sleep mode	Wait	In Wait mode, all peripheral modules are operational. The MCU core is placed into Sleep mode.				
	Very Low Power Wait	In VLPW mode, all peripheral modules are operational at a reduced frequency except the Low Voltage Detect (LVD) monitor, which is disabled. The MCU core is placed into Sleep mode.				
Deep sleep	Stop	In Stop mode, most peripheral clocks are disabled and placed in a static state. Stop mode retains all registers and SRAMs while maintaining Low Voltage Detection protection. In Stop mode, the ADC, CMP, LPTMR, RTC, and pin interrupts are operational. The NVIC is disabled, but the AWIC can be used to wake up from an interrupt.				
	Very Low Power Stop	In VLPS mode, the contents of the SRAM are retained. The CMP (low speed), ADC, OSC, LPTMR, LPIT, FlexIO, LPUART, LPI2C, LPSPI, and RTC.				
		DMA are operational, LVD and NVIC are disabled, AWIC is used to wake up from interrupt.				

Table 7. Peripherals states in different operational modes

2.1.9 Debug controller

This device has extensive debug capabilities including run control and tracing capabilities. The standard ARM debug port supports SWD interface.

2.2 Peripheral features

The following sections describe the features of each peripherals of the chip.

2.2.1 eDMA and DMAMUX

The eDMA is a highly programmable data-transfer engine optimized to minimize any required intervention from the host processor. It is intended for use in applications where the data size to be transferred is statically known and not defined within the transferred data itself. The DMA controller in this device implements 8 channels which can be routed from up to 63 DMA request sources through DMAMUX module.

Main features of eDMA are listed below:

- All data movement via dual-address transfers: read from source, write to destination
- 8-channel implementation that performs complex data transfers with minimal intervention from a host processor
- Transfer control descriptor (TCD) organized to support two-deep, nested transfer operations
 - Channel activation via one of three methods
 - Fixed-priority and round-robin channel arbitration
 - Channel completion reported via programmable interrupt requests
 - Programmable support for scatter/gather DMA processing
 - Support for complex data structures

2.2.2 FTM

This device contains three FlexTimer modules.

The FlexTimer module (FTM) is a two-to-eight channel timer that supports input capture, output compare, and the generation of PWM signals to control electric motor and power management applications. The FTM time reference is a 16-bit counter that can be used as an unsigned or signed counter.

Several key enhancements of this module are made:

- Signed up counter
- Deadtime insertion hardware
- · Fault control inputs
- · Enhanced triggering functionality
- Initialization and polarity control

2.2.3 ADC

This device contains one 12-bit SAR ADC module. The ADC module supports hardware triggers from FTM, LPTMR, LPIT, external trigger pin, RTC, and CMP output. It supports wakeup of MCU in low power mode when using internal clock source or external crystal clock.

ADC module has the following features:

- Linear successive approximation algorithm with up to 12-bit resolution
- · Up to single-ended external analog inputs

- · Support 12-bit, 10-bit, and 8-bit single-ended output modes
- · Single or continuous conversion
- · Configurable sample time and conversion speed/power
- · Input clock selectable from up to four sources
- · Operation in low-power modes for lower noise
- · Selectable hardware conversion trigger
- Automatic compare with interrupt for less-than, greater-than or equal-to, within range, or out-of-range, programmable value
- Temperature sensor
- · Hardware average function
- · Selectable Voltage reference: from external or alternate
- · Self-Calibration mode

2.2.3.1 Temperature sensor

This device contains one temperature sensor internally connected to the input channel of AD26, see ADC electrical specifications for details of the linearity factor.

The sensor must be calibrated to gain good accuracy, so as to provide good linearity, see also AN3031 for more detailed application information of the temperature sensor.

2.2.4 CMP

There is one analog comparator on this device.

- Each CMP has its own independent 8-bit DAC.
- · Each CMP supports up to 6 analog inputs from external pins.
- · Each CMP is able to convert an internal reference from the bandgap.
- Each CMP supports the round-robin sampling scheme. In summary, this allow the CMP to operate independently in VLPS and Stop modes, whilst being triggered periodically to sample up to 6 inputs. Only if an input changes state is a full wakeup generated.

The CMP has the following features:

- · Inputs may range from rail to rail
- · Programmable hysteresis control
- · Selectable interrupt on rising-edge, falling-edge, or both rising and falling edges of the comparator output
- · Selectable inversion on comparator output
- · Capability to produce a wide range of outputs such as sampled, windowed, or digitally filtered
- · External hysteresis can be used at the same time that the output filter is used for internal functions
- Two software selectable performance levels: Shorter propagation delay at the expense of higher power, and Low power with longer propagation delay
- DMA transfer support
- · Functional in all power modes available on this MCU
- The window and filter functions are not available in STOP mode
- Integrated 8-bit DAC with selectable supply reference source and can be power down to conserve power

2.2.5 LPIT

The Low Power Periodic Interrupt Timer (LPIT) is a multi-channel timer module generating independent pre-trigger and trigger outputs. These timer channels can operate individually or can be chained together. The LPIT can operate in low power modes if configured to do so. The pre-trigger and trigger outputs can be used to trigger other modules on the device.

2.2.6 LPTMR

The low-power timer (LPTMR) can be configured to operate as a time counter with optional prescaler, or as a pulse counter with optional glitch filter, across all power modes, including the low-leakage modes. It can also continue operating through most system reset events, allowing it to be used as a time of day counter.

The LPTMR module has the following features:

- 16-bit time counter or pulse counter with compare
 - Optional interrupt can generate asynchronous wakeup from any low-power mode
 - Hardware trigger output
 - Counter supports free-running mode or reset on compare
- · Configurable clock source for prescaler/glitch filter
- · Configurable input source for pulse counter

2.2.7 CRC

This device contains one cyclic redundancy check (CRC) module which can generate 16/32-bit CRC code for error detection.

The CRC module provides a programmable polynomial, WAS, and other parameters required to implement a 16-bit or 32-bit CRC standard.

The CRC module has the following features:

- · Hardware CRC generator circuit using a 16-bit or 32-bit programmable shift register
- · Programmable initial seed value and polynomial
- Option to transpose input data or output data (the CRC result) bitwise or bytewise.
- · Option for inversion of final CRC result
- · 32-bit CPU register programming interface

2.2.8 LPUART

This product contains three Low-Power UART modules, and can work in Stop and VLPS modes. The module also supports 4× to 32× data oversampling rate to meet different applications.

The LPUART module has the following features:

- Programmable baud rates (13-bit modulo divider) with configurable oversampling ratio from 4× to 32×
- Transmit and receive baud rate can operate asynchronous to the bus clock and can be configured independently of the bus clock frequency, support operation in Stop mode
- Interrupt, DMA or polled operation
- · Hardware parity generation and checking
- · Programmable 8-bit, 9-bit or 10-bit character length
- · Programmable 1-bit or 2-bit stop bits
- Three receiver wakeup methods
 - Idle line wakeup

- Address mark wakeup
- Receive data match
- · Automatic address matching to reduce ISR overhead:
 - Address mark matching
 - Idle line address matching
 - Address match start, address match end
- Optional 13-bit break character generation / 11-bit break character detection
- · Configurable idle length detection supporting 1, 2, 4, 8, 16, 32, 64 or 128 idle characters
- · Selectable transmitter output and receiver input polarity

2.2.9 SCI

This device contains two SCI modules to provide more UART ports with minimum die size increase.

The SCI modules have the following features:

- · Support standard UART features
- · Two SCI modules support both LIN operation
- Support DMA

2.2.10 LPSPI

This device contains one LPSPI module. The LPSPI is a low power Serial Peripheral Interface (SPI) module that supports an efficient interface to an SPI bus as a master and/or a slave. The LPSPI can continue operating in stop modes provided an appropriate clock is available and is designed for low CPU overhead with DMA offloading of FIFO register accesses.

The LPSPI module has the following features:

- Command/transmit FIFO of 4 words
- Receive FIFO of 4 words
- · Host request input can be used to control the start time of an SPI bus transfer

2.2.11 LPI2C

This device contains one LPI2C module. The LPI2C is a low power Inter-Integrated Circuit (I2C) module that supports an efficient interface to an I2C bus as a master and/or a slave. The LPI2C can continue operating in stop modes provided an appropriate clock is available and is designed for low CPU overhead with DMA offloading of FIFO register accesses. The LPI2C implements logic support for standard-mode, fast-mode, fast-mode plus and ultra-fast modes of operation. The LPI2C module also complies with the *System Management Bus (SMBus) Specification, version 2*.

The LPI2C modules have the following features:

- Standard, Fast, Fast+ and Ultra Fast modes are supported
- · HS-mode supported in slave mode
- · Multi-master support including synchronization and arbitration
- Clock stretching
- · General call, 7-bit and 10-bit addressing
- Software reset, START byte and Device ID require software support
- · For master mode:
 - command/transmit FIFO of 4 words

- receive FIFO of 4 words
- · For slave mode:
 - separate I2C slave registers to minimize software overhead due to master/ slave switching
 - support for 7-bit or 10-bit addressing, address range, SMBus alert and general call address
 - transmit/receive data register supporting interrupt or DMA requests

2.2.12 FlexIO

The FlexIO is a highly configurable module providing a wide range of protocols including, but not limited to UART, I2C, SPI, Camera IF, LCD RGB, PWM/Waveform generation. The module supports programmable baud rates independent of bus clock frequency, with automatic start/stop bit generation.

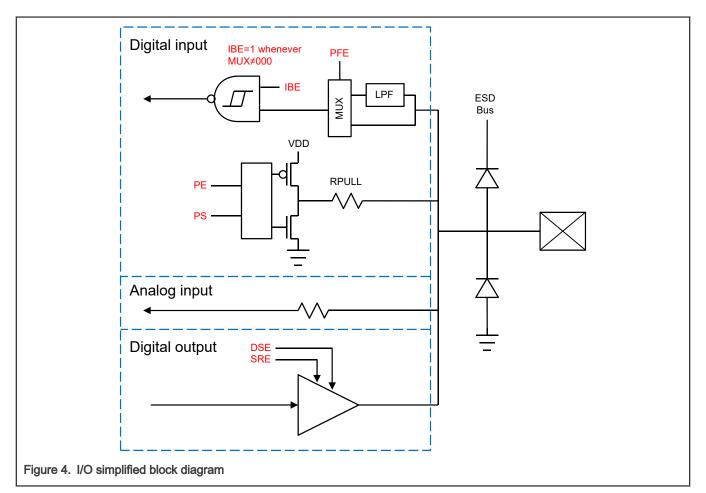
The FlexIO module has the following features:

- · Functional in VLPR/VLPW/Stop/VLPS mode provided the clock it is using remains enabled
- · Four 32-bit double buffered shift registers with transmit, receive, and data match modes, and continuous data transfer
- The timing of the shifter's shift, load and store events are controlled by the highly flexible 16-bit timer assigned to the shifter
- · Two or more shifters can be concatenated to support large data transfer sizes
- Each 16-bit timers operates independently, supports for reset, enable and disable on a variety of internal or external trigger conditions with programmable trigger polarity
- · Flexible pin configuration supporting output disabled, open drain, bidirectional output data and output mode
- Supports interrupt, DMA or polled transmit/receive operation

2.2.13 Port control and GPIO

The Port Control and Interrupt (PORT) module provides support for port control, digital filtering, and external interrupt functions. The GPIO data direction and output data registers control the direction and output data of each pin when the pin is configured for the GPIO function. The GPIO input data register displays the logic value on each pin when the pin is configured for any digital function, provided the corresponding Port Control and Interrupt module for that pin is enabled.

The following figure shows the basic I/O pad structure. Pseudo open-drain pins have the p-channel output driver disabled when configured for open-drain operation. None of the I/O pins, including open-drain and pseudo open-drain pins, are allowed to go above VDD.



The PORT module has the following features:

- All PIN support interrupt enable
- · Configurable edge (rising, falling, or both) or level sensitive interrupt type
- Support DMA request
- · Asynchronous wake-up in low-power modes
- · Configurable pullup, pulldown, and pull-disable on select pins
- · Configurable high and low drive strength on selected pins
- Configurable passive filter on selected pins
- Individual mux control field supporting analog or pin disabled, GPIO, and up to chip-specific digital functions
- Pad configuration fields are functional in all digital pin muxing modes.

The GPIO module has the following features:

- · Port Data Input register visible in all digital pin-multiplexing modes
- · Port Data Output register with corresponding set/clear/toggle registers
- Port Data Direction register
- GPIO support single-cycle access via fast GPIO.

2.2.14 TSI

This device contains two TSI modules. TSI provides touch sensing detection on capacitive touch sensors. The external capacitive touch sensor is typically formed on PCB and the sensor electrodes are connected to TSI input channels through the I/O pins in the device.

TSI operates in switching integration mode to achieve low-power, high-sensitivity, and advanced EMC robustness. It supports both self-cap and mutual-cap sensors. In self-cap mode, TSI requires only one pin for each touch sensor. In mutual-cap mode, sensing is done with using capacitive touch matrix in various Tx-Rx configurations. TSI requires one pin per Tx line and one pin per Rx line.

TSI features are as follows:

- Advanced EMC robustness
- · Supports both self-cap sensor and mutual-cap sensor
- · One pin per electrode no external components
- Adjustable touch sensing resolution and sensitivity for sensing a variety of overlay materials and thicknesses
- Low power consumption
- · Capability to wake up MCU from low power modes for low power application
- · Supports DMA data transfer
- Fully supports NXP touch library, see NXP touch library for details.
- Each TSI channel configurable to function as the scan channel or shield channel

3 Memory map

This device contains various memories and memory-mapped peripherals which are located in a 4 GB memory space. For more details of the system memory and peripheral locations, see the Memory Map chapter in the Kinetis KE17Z/13Z/12Z with up to 512 KB Flash Reference Manual.

4 Pinouts

4.1 KE1xZ Signal Multiplexing and Pin Assignments

The following table shows the signals available on each pin and the locations of these pins on the devices supported by this document. The Port Control Module is responsible for selecting which ALT functionality is available on each pin.

10 0 L Q FP	64 L Q FP	Pin Name	Default	ALT0	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7
1	_	PTE16	TSI0_CH13	TSI0_CH13	PTE16					FXIO_D3	TRGMUX _ OUT7
2		PTE15	TSI0_CH14	TSI0_CH14	PTE15					FXIO_D2	TRGMUX _ OUT6

Table 8. Pin assignments

Table continues on the next page ...

3	1	PTD1	TSI0_CH11	TSI0_CH11	PTD1	FTM0_CH3	LPSPI1_ SIN	FTM2_C H1	FXIO_D1	TRGMUX _ OUT2
4	2	PTD0	TSI0_CH12	TSI0_CH12	PTD0	FTM0_CH2	LPSPI1_ SCK	FTM2_C H0	FXIO_D0	TRGMUX _ OUT1
5	3	PTE11	TSI0_CH9	TSI0_CH9	PTE11	PWT_IN1	LPTMR0 _ ALT1		FXIO_D5	TRGMUX _ OUT5
6	4	PTE10	TSI0_CH10	TSI0_CH10	PTE10	CLKOUT			FXIO_D4	TRGMUX _ OUT4
7	_	PTE13	TSI0_CH15	TSI0_CH15	PTE13					TRGMUX _ OUT5
8	5	PTE5	TSI0_CH16	TSI0_CH16	PTE5	TCLK2		FTM2_C H3	FXIO_D7	EWM_IN
9	6	PTE4	TSI0_CH17	TSI0_CH17	PTE4	BUSOUT		FTM2_C H2	FXIO_D6	EWM_O UT_b
10	7	VDD	VDD	VDD						
11	8	VDDA	VDDA	VDDA						
12	9	VREF H	VREFH	VREFH						
	10	VSS/ VREFL	VSS/ VREFL	VSS/ VREFL						
13		VREFL	VREFL	VREFL						
14		VSS	VSS	VSS						
15	11	PTB7	EXTAL	EXTAL	PTB7	LPI2C0_SC L	LPUART 0_TX			
16	12	PTB6	XTAL	XTAL	PTB6	LPI2C0_SD A	LPUART 0_RX			
17		PTE14	DISABLED		PTE14	FTM0_FLT 1				TRGMUX _ OUT4
18	13	PTE3	ADC0_SE6/ TSI0_CH18	ADC0_SE6/ TSI0_CH18	PTE3	FTM0_FLT 0	LPUART 2_ RTS		TRGMUX _IN6	
19		PTE12	DISABLED		PTE12	FTM0_FLT 3	LPUART 2_TX			TRGMUX _ OUT3
20		PTD17	DISABLED		PTD17	FTM0_FLT 2	LPUART 2_RX			TRGMUX _ OUT2

Table continues on the next page...

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21	14	PTD16	ADC0_SE4/ TSI0_CH19	ADC0_SE4/ TSI0_CH19	PTD16	FTM0_CH1					
22	15	PTD15	ADC0_SE2/ TSI0_CH20	ADC0_SE2/ TSI0_CH20	PTD15	FTM0_CH0					
23	16	PTE9	ADC0_SE0/ TSI0_CH21	ADC0_SE0/ TSI0_CH21	PTE9	FTM0_CH7	LPUART 2_ CTS				
24	_	PTD14	DISABLED		PTD14		LPUART 1_TX				CLKOUT
25	_	PTD13	DISABLED		PTD13		LPUART 1_RX				RTC_CL KOUT
26	17	PTE8	CMP0_IN3/ ADC0_SE1/ TSI0_CH22	CMP0_IN3/ ADC0_SE1/ TSI0_CH22	PTE8	FTM0_CH6					
27	18	PTB5	ADC0_SE3/ TSI0_CH23	ADC0_SE3/ TSI0_CH23	PTB5	FTM0_CH5	LPSPI0_ PCS1			TRGMUX _IN0	
28	19	PTB4	ADC0_SE5/ TSI0_CH24	ADC0_SE5/ TSI0_CH24	PTB4	FTM0_CH4	LPSPI0_ SOUT			TRGMUX _IN1	
29	20	PTC3	ADC0_SE7/ CMP0_IN4	ADC0_SE7/ CMP0_IN4	PTC3	FTM0_CH3				FXIO_D7	
30	21	PTC2	ADC0_SE1 5/ CMP0_IN5	ADC0_SE1 5/ CMP0_IN5	PTC2	FTM0_CH2				FXIO_D6	
31	22	PTD7	ADC0_SE1 3	ADC0_SE1 3	PTD7	LPUART2_ TX					
32	23	PTD6	ADC0_SE1 1	ADC0_SE1 1	PTD6	LPUART2_ RX					
33	24	PTD5	ADC0_SE9	ADC0_SE9	PTD5	FTM2_CH3	LPTMR0 _ ALT2	FXIO_D3	PWT_IN2	TRGMUX _IN7	LPUART 2_ CTS
34	_	PTD12	DISABLED		PTD12	FTM2_CH2	LPI2C1_ HREQ			LPUART 2_ RTS	
35	—	PTD11	DISABLED		PTD11	FTM2_CH1				LPUART 2_ CTS	
36	_	PTD10	DISABLED		PTD10	FTM2_CH0					
37	_	VSS	VSS	VSS							
38	_	VDD	VDD	VDD							

Table continues on the next page ...

							-				
39	25	PTC1	ADC0_SE8/ TSI1_CH24	ADC0_SE8/ TSI1_CH24	PTC1	FTM0_CH1		SCI0_TX			
40	26	PTC0	ADC0_SE1 0/ TSI1_CH23	ADC0_SE1 0/ TSI1_CH23	PTC0	FTM0_CH0		SCI0_RX			
41		PTD9	DISABLED		PTD9		LPI2C1_ SCL			FXIO_D2	
42	_	PTD8	DISABLED		PTD8	FTM0_CH7	LPI2C_S DA		LPSPI0_ PCS1		
43	27	PTC17	ADC0_SE1 2/ TSI1_CH22	ADC0_SE1 2/ TSI1_CH22	PTC17			LPI2C1_ SCLS		SCI1_TX	
44	28	PTC16	ADC0_SE1 4/ TSI1_CH21	ADC0_SE1 4/ TSI1_CH21	PTC16			LPI2C1_ SDAS		SCI1_RX	
45	29	PTC15	ADC0_SE1 6/ TSI1_CH20	ADC0_SE1 4/ TSI1_CH20	PTC15	FTM1_CH3		SCI0_TX			
46	30	PTC14	ADC0_SE1 7/ TSI1_CH19	ADC0_SE1 7/ TSI1_CH19	PTC14	FTM1_CH2		SCI0_RX			
47	31	PTB3	ADC0_SE1 8/ TSI1_CH18	ADC0_SE1 8/ TSI1_CH18	PTB3	FTM1_CH1	LPSPI0_ SIN			TRGMUX _IN2	
48	32	PTB2	ADC0_SE1 9/ TSI1_CH17	ADC0_SE1 9/ TSI1_CH17	PTB2	FTM1_CH0	LPSPI0_ SCK			TRGMUX _IN3	
49	_	PTC13	DISABLED		PTC13				LPSPI0_ PCS0		
50	_	PTC12	DISABLED		PTC12				LPSPI0_ SOUT		
51	_	PTC11	DISABLED		PTC11				LPSPI0_ SIN		
52	_	PTC10	DISABLED		PTC10				LPSPI0_ SCK		
53	33	PTB1	ADC0_SE2 0/ TSI1_CH16	ADC0_SE2 0/ TSI1_CH16	PTB1	LPUART0_ TX	LPSPI0_ SOUT	TCLK0			

Table continues on the next page...

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		-		,							
54	34	PTB0	ADC0_SE2 1/ TSI1_CH15	ADC0_SE2 1/ TSI1_CH15	PTB0	LPUART0_ RX	LPSPI0_ PCS0	LPTMR0 _ ALT3	PWT_IN3		
55	35	PTC9	ADC0_SE2 2/ TSI1_CH14	ADC0_SE2 2/ TSI1_CH14	PTC9	LPUART1_ TX				LPUART 0_ RTS	
56	36	PTC8	ADC0_SE2 4/ TSI1_CH13	ADC0_SE2 4/ TSI1_CH13	PTC8	LPUART1_ RX				LPUART 0_ CTS	
57	37	PTA7	TSI1_CH12	TSI1_CH12	PTA7	FTM0_FLT 2	LPSPI0_ PCS3	RTC_ CLKIN		LPUART 1_ RTS	
58	38	PTA6	TSI1_CH11	TSI1_CH11	PTA6	FTM0_FLT 1	LPSPI1_ PCS1			LPUART 1_ CTS	
59	39	PTE7	TSI1_CH10	TSI1_CH10	PTE7	FTM0_CH7					
60	40	VSS	VSS	VSS							
61	41	VDD	VDD	VDD							
62	_	PTA17	DISABLED		PTA17	FTM0_CH6		EWM_O UT_b			
63	_	PTB17	DISABLED		PTB17	FTM0_CH5	LPSPI1_ PCS3				
64	_	PTB16	DISABLED		PTB16	FTM0_CH4	LPSPI1_ SOUT				
65	_	PTB15	DISABLED		PTB15	FTM0_CH3	LPSPI1_ SIN				
66	_	PTB14	DISABLED		PTB14	FTM0_CH2	LPSPI1_ SCK				
67	42	PTB13	TSI1_CH9	TSI1_CH9	PTB13	FTM0_CH1				SCI1_TX	
68	43	PTB12	TSI1_CH8	TSI1_CH8	PTB12	FTM0_CH0				SCI1_RX	
69	44	PTD4	TSI1_CH7	TSI1_CH7	PTD4	FTM0_FLT 3					
70	45	PTD3	NMI_b		PTD3		LPSPI1_ PCS0	FXIO_D5	LPI2C0_ SCL	TRGMUX _IN4	NMI_b
71	46	PTD2	TSI1_CH6	TSI1_CH6	PTD2		LPSPI1_ SOUT	FXIO_D4	LPI2C0_ SDA	TRGMUX _IN5	

Table continues on the next page ...

Table 8. Pin assignments (continued)

		-	-	-	1				1		
72	47	PTA3	TSI1_CH5	TSI1_CH5	PTA3		LPI2C0_ SCL	EWM_IN		LPUART 0_TX	
73	48	PTA2	TSI1_CH4	TSI1_CH4	PTA2		LPI2C0_ SDA	EWM_O UT_b		LPUART 0_RX	
74	_	PTB11	DISABLED		PTB11	FTM0_CH1	LPI2C0_ HREQ			FXIO_D1	
75	_	PTB10	DISABLED		PTB10	FTM0_CH0	LPI2C0_ SDAS			FXIO_D0	
76	_	PTB9	DISABLED		РТВ9		LPI2C0_ SCLS			FXIO_D5	
77		PTB8	DISABLED		PTB8			LPI2C0_ SCL		FXIO_D4	
78	49	PTA1	CMP0_IN1/ TSI1_CH3	CMP0_IN1/ TSI1_CH3	PTA1	FTM1_CH1	LPI2C0_ SDAS	FXIO_D3		LPUART 0_ RTS	TRGMUX _ OUT0
79	50	PTA0	CMP0_IN0/ TSI1_CH2	CMP0_IN0/ TSI1_CH2	PTA0	FTM2_CH1	LPI2C0_ SCLS	FXIO_D2		LPUART 0_ CTS	TRGMUX _ OUT3
80	51	PTC7	TSI1_CH1	TSI1_CH1	PTC7	LPUART1_ TX					
81	52	PTC6	TSI1_CH0	TSI1_CH0	PTC6	LPUART1_ RX					
82	—	PTA16	DISABLED		PTA16	FTM1_CH3	LPSPI0_ PCS2	LPI2C0_ SDA			
83	—	PTA15	DISABLED		PTA15	FTM1_CH2	LPSPI0_ PCS3				
84	53	PTE6	TSI0_CH0	TSI0_CH0	PTE6	LPSPI0_ PCS2				LPUART 1_ RTS	
85	54	PTE2	TSI0_CH1	TSI0_CH1	PTE2	LPSPI0_ SOUT	LPTMR0 _ ALT3		PWT_IN3	LPUART 1_ CTS	
86		VSS	VSS	VSS							
87		VDD	VDD	VDD							
88	_	PTA14	DISABLED		PTA14	FTM0_FLT 0		EWM_IN			BUSOUT
89	55	PTA13	TSI0_CH2	TSI0_CH2	PTA13			LPI2C1_ SCLS	LPUART 0_RX		

Table continues on the next page ...

Table 8. Pin assignments (continued)

			1	1		1		1	1	
90	56	PTA12	TSI0_CH3	TSI0_CH3	PTA12			LPI2C1_ SDAS	LPUART 0_TX	
91	57	PTA11	TSI0_CH4	TSI0_CH4	PTA11		LPUART 0_RX	FXIO_D1		
92	58	PTA10	TSI0_CH5	TSI0_CH5	PTA10		LPUART 0_TX	FXIO_D0		
93	59	PTE1	TSI0_CH6	TSI0_CH6	PTE1	LPSPI0_SI N	LPI2C0_ HREQ	LPI2C1_ SCL		
94	60	PTE0	TSI0_CH7	TSI0_CH7	PTE0	LPSPI0_SC K	TCLK1	LPI2C1_ SDA		
95	61	PTC5	TSI0_CH8	TSI0_CH8	PTC5	FTM2_CH0	RTC_CL KOUT	LPI2C1_ HREQ		
96	62	PTC4	SWD_CLK	CMP0_IN2	PTC4	FTM1_CH0	LPUART 1_RX		EWM_IN	SWD_CL K
97	63	PTA5	RESET_b		PTA5		TCLK1			RESET_ b
98	64	PTA4	SWD_DIO		PTA4		LPUART 1_TX	CMP0_O UT	EWM_O UT_b	SWD_DI O
99	_	PTA9	DISABLED		PTA9			FXIO_D7		TRGMUX _ OUT1
10 0		PTA8	DISABLED		PTA8			FXIO_D6		TRGMUX _ OUT0

NOTE

Each TSI channel can be configured as TSI shield channel.

4.2 Port control and interrupt summary

The following table provides more information regarding the Port Control and Interrupt configurations.

Table 9. Ports summary	
------------------------	--

Feature	Port A	Port B	Port C	Port D	Port E
Pull select control	Yes	Yes	Yes	Yes	Yes
Pull select at reset	PTA4/PTA5=Pull up, Others=No	No	PTC4=Pull down, Others=No	PTD3=Pull up, Others=No	No
Pull enable control	Yes	Yes	Yes	Yes	Yes

Table continues on the next page ...

Pull enable at reset	PTA4/ PTA5=Enabled; Others=Disabled	Disabled	PTC4=Enabled; Others=Disabled	PTD3=Enabled; Others=Disabled	Disabled
Passive filter enable control	PTA5=Yes; Others=No	No	No	PTD3=Yes; Others=No	No
Passive filter enable at reset	PTA5=Enabled; Others=Disabled	Disabled	Disabled	Disabled	Disabled
Open drain enable control	I2C and UART Tx=Enabled; Others=Disabled				
Open drain enable at reset	Disabled	Disabled	Disabled	Disabled	Disabled
Drive strength enable control	No	PTB4/PTB5 only	No	PTD0/PTD1/ PTD15/PTD16 only	PTE0/PTE1 only
Drive strength enable at reset	Disabled	Disabled	Disabled	Disabled	Disabled
Pin mux control	Yes	Yes	Yes	Yes	Yes
Pin mux at reset	PTA4/PTA5=ALT7; Others=ALT0	ALT0	PTC4=ALT7; Others=ALT0	PTD3=ALT7; Others=ALT0	ALT0
Lock bit	Yes	Yes	Yes	Yes	Yes
Interrupt and DMA request	Yes	Yes	Yes	Yes	Yes
Digital glitch filter	No	No	No	No	Yes

4.3 Module Signal Description Tables

The following sections correlate the chip-level signal name with the signal name used in the module's chapter. They also briefly describe the signal function and direction.

4.3.1 SWD signal module

Table 10. SWD signal descriptions

Chip signal name	Module signal name	Description	I/O
SWD_CLK	SWD_CLK	Serial Wire Clock	I
SWD_DIO	SWD_DIO	Serial Wire Data	I/O

4.3.2 System modules

Tahla	11	System	eignal	description
able	1.1.1	System	Signal	description

Chip signal name	Module signal name	Description	I/O
NMI_b	_	Non-maskable interrupt NOTE: Driving the NMI signal low forces a non-maskable interrupt, if the NMI function is selected on the corresponding pin.	I
RESET_b	_	Reset bidirectional signal	I/O
VDD	_	MCU power	I
VSS	_	MCU ground	I

Table 12. EWM signal descriptions

Chip signal name	Module signal name	Description	I/O
EWM_IN	EWM_in	EWM input for safety status of external safety circuits. The polarity of EWM_IN is programmable using the EWM_CTRL[ASSIN] bit. The default polarity is active-low.	I
EWM_OUT_b	EWM_out	EWM reset out signal	0

4.3.3 Clock modules

Table 13. OSC (in SCG) signal descriptions

Chip signal name	Module signal name	Description	I/O
EXTAL	EXTAL	External clock/Oscillator input	I
XTAL	XTAL	Oscillator output	0

4.3.4 Analog modules

Table 14. ADC0 signal descriptions

Chip signal name	Module signal name	Description	I/O
ADC <i>0</i> _SE[23:0]	AD[23:0]	Single-Ended Analog Channel Inputs	I
VREFH	VREFSH	Voltage Reference Select High	I
VREFL	VREFSL	Voltage Reference Select Low	I
VDDA	VDDA	Analog Power Supply	I

General Business Information

Table 15. CMP0 signal descriptions

Chip signal name	Module signal name	Description	I/O
CMP <i>0</i> _IN[5:0]	IN[5:0]	Analog voltage inputs	I
CMP0_OUT	СМРО	Comparator output	0

4.3.5 Timer modules

Table 16. LPTMR0 signal descriptions

Chip signal name	Module signal name	Description	I/O
LPTMR0_ALT[3:1]	LPTMR_ALT <i>n</i>	Pulse Counter Input pin	I

Table 17. FTM0 signal descriptions

Chip signal name	Module signal name	Description	I/O
FTM <i>0</i> _CH[7:0]	CHn	FTM channel (n), where n can be 7-0	I/O
FTM <i>0</i> _FLT[3:0]	FAULTj	Fault input (j), where j can be 3-0	I
TCLK[2:0]	EXTCLK	External clock. FTM external clock can be selected to drive the FTM counter.	I

Table 18. FTM 1 signal descriptions

Chip signal name	Module signal name	Description	I/O
FTM1_CH[3:0]	CHn	FTM channel (n), where n can be 3-0	I/O
FTM 1_FLT[3:2]	FAULTj	Fault input (j), where j can be 3-2	I
TCLK[2:0]	EXTCLK	External clock. FTM external clock can be selected to drive the FTM counter.	I

Table 19. FTM2 signal descriptions

Chip signal name	Module signal name	Description	I/O
FTM2_CH[3:0]	CHn	FTM channel (n), where n can be 3-0	I/O
FTM2_FLT[3:2]	FAULTj	Fault input (j), where j can be 3-2	I
TCLK[2:0]	EXTCLK	External clock. FTM external clock can be selected to drive the FTM counter.	I

4.3.6 Communication interfaces

Table 20.	LPSPIn signal	descriptions

Chip signal name	Module signal name	Description	I/O
LPSPIn_SOUT	SOUT	Serial Data Out	0
LPSPIn_SIN	SIN	Serial Data In	I
LPSPIn_SCK	SCK	Serial Clock	I/O
LPSPIn_PCS[3:0]	PCS[3:0]	Peripheral Chip Select 0-3	I/O

Table 21. SCIn signal descriptions

Chip signal name	Module signal name	Description	I/O
SCI <i>n</i> _TX	TXD	Transmit data	0
SCI <i>n</i> _RX	RXD	Receive data	0

Table 22. LPI2Cn signal descriptions

Chip signal name	Module signal name	Description	I/O
LPI2Cn_SCL	SCL	Bidirectional serial clock line of the I2C system.	I/O
LPI2Cn_SDA	SDA	Bidirectional serial data line of the I2C system.	I/O
LPI2C <i>n_</i> HREQ	HREQ	Host request, can initiate an LPI2C master transfer if asserted and the I2C bus is idle.	I
LPI2Cn_SCLS	SCLS	Secondary I2C clock line.	I/O
LPI2Cn_SDAS	SDAS	Secondary I2C data line.	I/O

Table 23. LPUARTn signal descriptions

Chip signal name	Module signal name	Description	I/O
LPUART <i>n</i> _TX	LPUART_TXD	Transmit data	I/O
LPUART <i>n</i> _RX	LPUART_RXD	Receive data	I
LPUART <i>n</i> _CTS	LPUART_CTS	Clear to send	I
LPUART <i>n</i> _RTS	LPUART_RTS	Request to send	0

Table 24. FlexIO signal descriptions

Chip signal name	Module signal name	Description	I/O
FXIO_D[7:0]	FXIO_D[7:0]	Bidirectional FlexIO Shifter and Timer pin inputs/outputs	I/O

4.3.7 Human-Machine interfaces

Table 25. GPIO signal descriptions

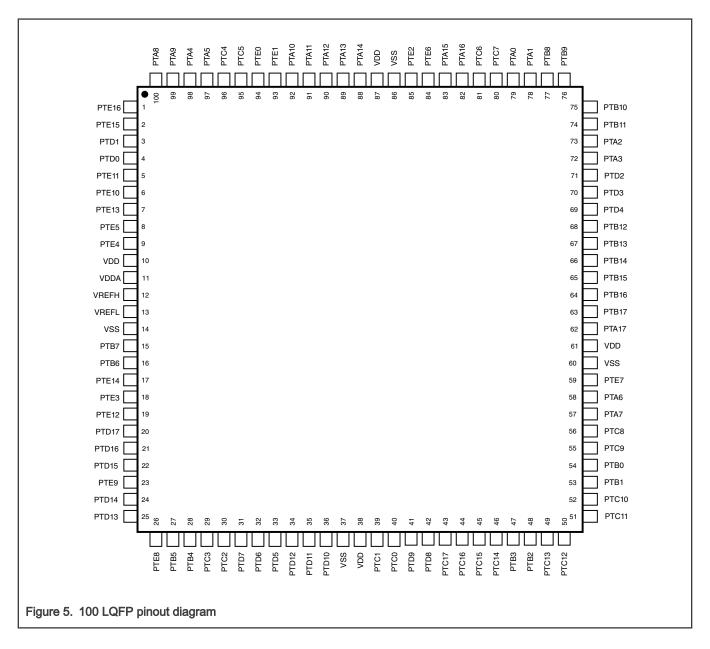
Chip signal name	Module signal name	Description	I/O
PTA[17:0]	PORTA17-PORTA0	General-purpose input/output	I/O
PTB[17:0]	PORTB17-PORTB0	General-purpose input/output	I/O
PTC[17:0]	PORTC17-PORTC0	General-purpose input/output	I/O
PTD[17:0]	PORTD17-PORTD0	General-purpose input/output	I/O
PTE[16:0]	PORTE16-PORTE0	General-purpose input/output	I/O

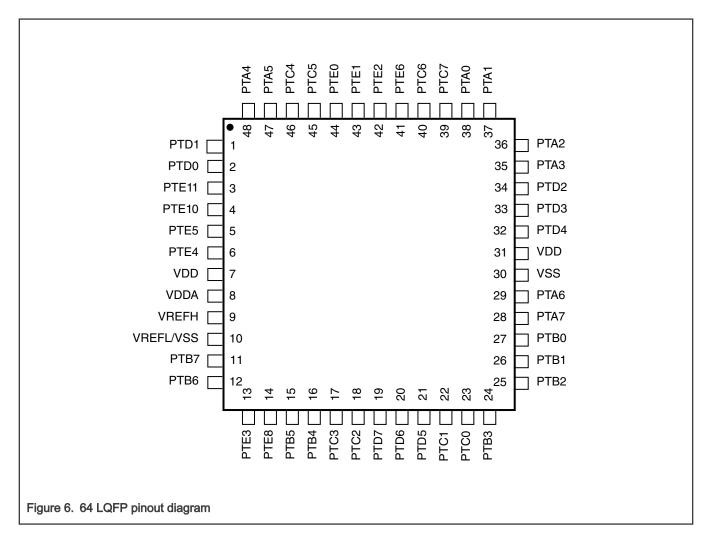
Table 26. TSI*n* signal descriptions

Chip signal name	Module signal name	Description	I/O
TSI <i>n</i> _CH[24:0]	TSI[24:0]	TSI sensing pins or GPIO pins	I/O

4.4 Pinout diagram

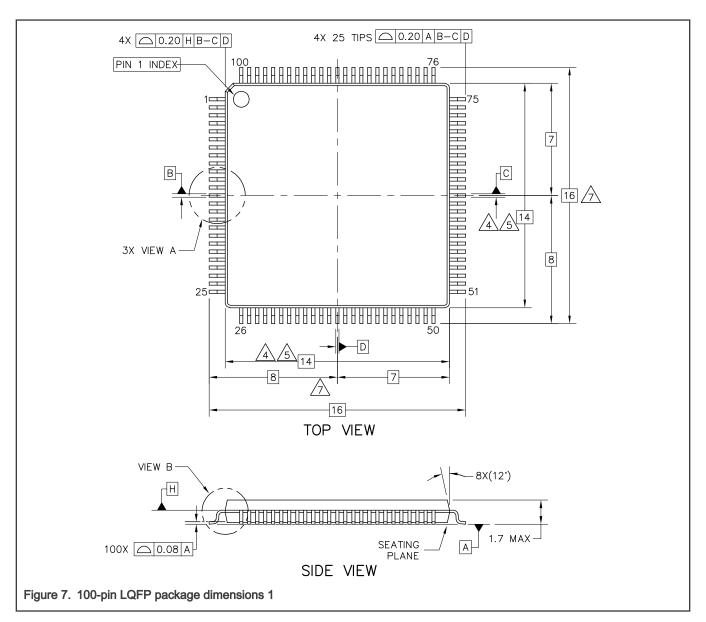
The following figure shows the pinout diagram for the devices supported by this document. Many signals may be multiplexed onto a single pin. To determine what signals can be used on which pin, see the previous table of Pin Assignments.

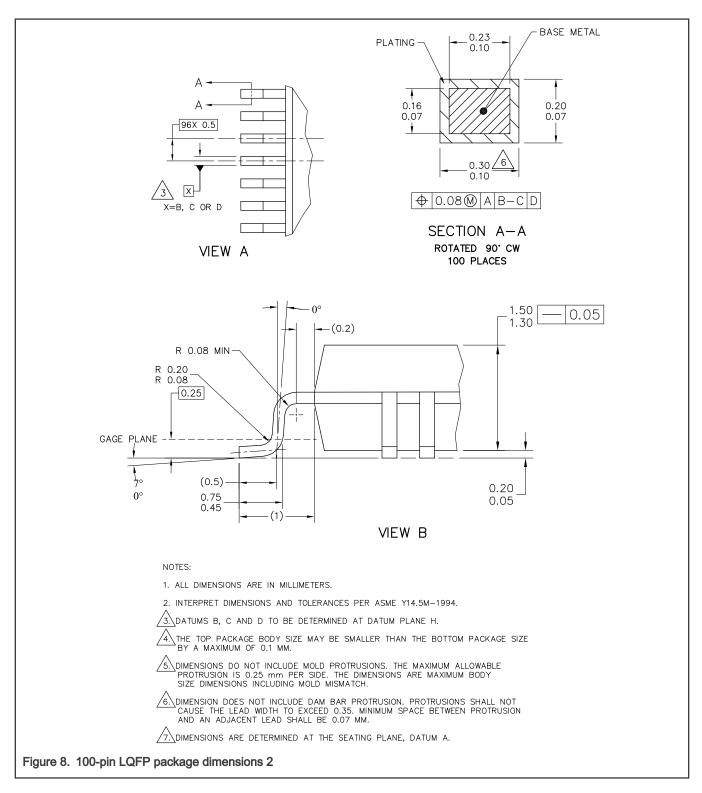


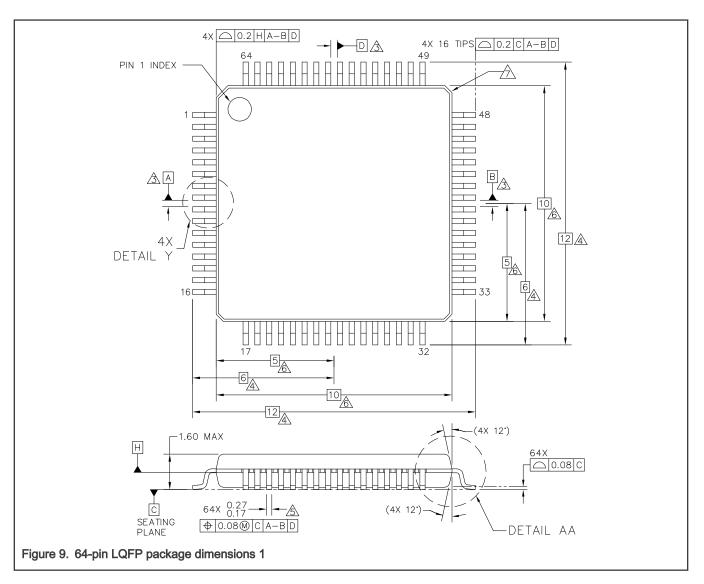


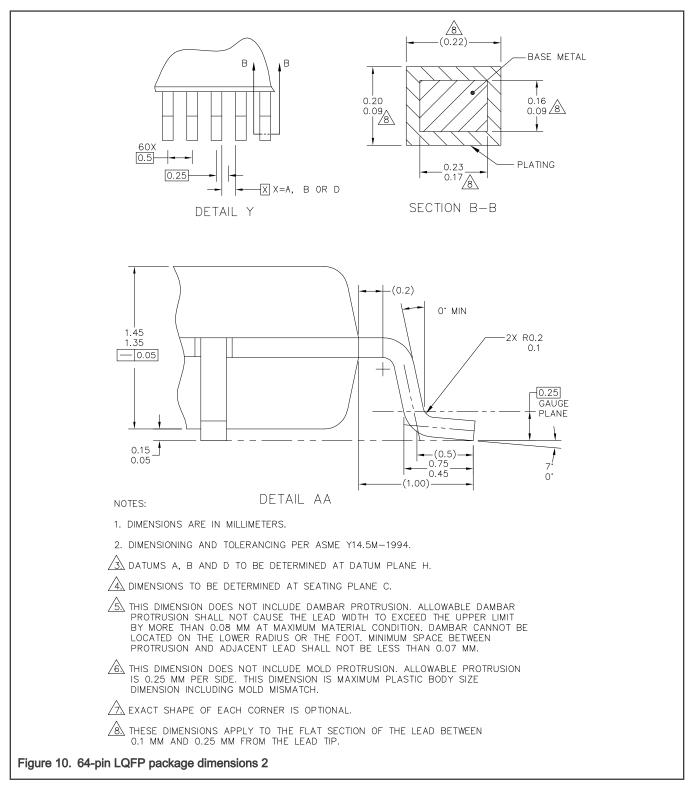
4.5 Package dimensions

The following figures show the dimensions of the package options for the devices supported by this document.









5 Electrical characteristics

5.1 Terminology and guidelines

5.1.1 Definitions

Key terms are defined in the following table:

Table 27. Definition

Term	Definition
Rating	A minimum or maximum value of a technical characteristic that, if exceeded, may cause permanent chip failure:
	Operating ratings apply during operation of the chip.
	Handling ratings apply when the chip is not powered.
	NOTE
	The likelihood of permanent chip failure increases rapidly as soon as a characteristic begins to exceed one of its operating ratings.
Operating requirement	A specified value or range of values for a technical characteristic that you must guarantee during operation to avoid incorrect operation and possibly decreasing the useful life of the chip
Operating behavior	A specified value or range of values for a technical characteristic that are guaranteed during operation if you meet the operating requirements and any other specified conditions
Typical value	A specified value for a technical characteristic that:
	Lies within the range of values specified by the operating behavior
	 Is representative of that characteristic during operation when you meet the Typical-value conditions or other specified conditions
	NOTE
	Typical values are provided as design guidelines and are neither tested nor guaranteed.

5.1.2 Examples

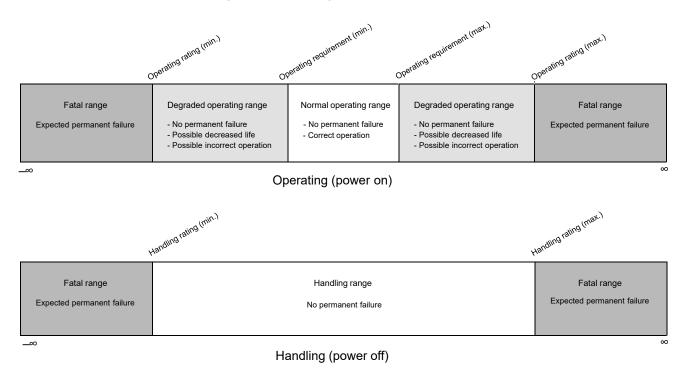
Symbol	Descript	ion	Min.	Max	κ.	Unit
	1.0 V core sup voltage	ply -0.3	1 AM	1.2	v	
			al -		ŀ	
erating req	uirement:			>		
Symbol	Descript	ion	Min.	Max	κ.	Unit
D	1.0 V core supp voltage	oly 0.9	A AMA	1.1	V	
		 				
anatina hal		a a trut a al	1			
erating beh	avior that include	s a typical va	ilue:			
erating beh	Description	es a <i>typical va</i>		yp.	Max.	Unit
_				yp. 130	Max. μA	Unit

5.1.3 Typical-value conditions

Typical values assume you meet the following conditions (or other conditions as specified):

Table 28. Typical-value conditions

Symbol	Description	Value	Unit
T _A	Ambient temperature	25	°C
VDD	Supply voltage	5.0	V



5.1.4 Relationship between ratings and operating requirements

5.1.5 Guidelines for ratings and operating requirements

Follow these guidelines for ratings and operating requirements:

- Never exceed any of the chip's ratings.
- During normal operation, don't exceed any of the chip's operating requirements.
- If you must exceed an operating requirement at times other than during normal operation (for example, during power sequencing), limit the duration as much as possible.

5.2 Ratings

5.2.1 Thermal handling ratings

Table 29. Thermal handling ratings

Symbol	Description	Min.	Max.	Unit	Notes
TSTG	Storage temperature	-55	150	°C	1
TSDR	Solder temperature, lead-free	_	260	°C	2

1. Determined according to JEDEC Standard JESD22-A103, High Temperature Storage Life.

2. Determined according to IPC/JEDEC Standard J-STD-020, *Moisture/Reflow Sensitivity Classification for Nonhermetic Solid State Surface Mount Devices*.

5.2.2 Moisture handling ratings

Table 30. Moisture handling ratings

Symbol	Description	Min.	Max.	Unit	Notes
MSL	Moisture sensitivity level	_	3	_	1

1. Determined according to IPC/JEDEC Standard J-STD-020, *Moisture/Reflow Sensitivity Classification for Nonhermetic Solid State Surface Mount Devices.*

5.2.3 ESD handling ratings

Table 31. ESD handling ratings

Symbol	Description	Min.	Max.	Unit	Notes
VHBM	Electrostatic discharge voltage, human body model	- 6000	6000	V	1
VCDM	Electrostatic discharge voltage, charged-device model				2
	All pins except the corner pins	- 500	500	V	
	Corner pins only	- 750	750	V	
ILAT	Latch-up current at ambient temperature upper limit	- 100	100	mA	3

1. Determined according to JEDEC Standard JS001, *Electrostatic Discharge (ESD) Sensitivity Testing Human Body Model (HBM)*.

2. Determined according to JEDEC Standard JS002, *Field-Induced Charged-Device Model Test Method for Electrostatic-Discharge-Withstand Thresholds of Microelectronic Components.*

3. Determined according to JEDEC Standard JESD78, IC Latch-Up Test.

5.2.4 Voltage and current operating ratings

NOTE

Functional operating conditions appear in the "DC electrical specifications". Absolute maximum ratings are stress ratings only, and functional operation at the maximum values is not guaranteed. Stress beyond the listed maximum values may affect device reliability or cause permanent damage to the device.

Table 32. Voltage and current operating ratings

Symbol	Description	Min.	Max.	Unit
VDD	Supply voltage	-0.3	5.8 ¹	V
IDD	Digital supply current	_	60	mA
VIO	IO pin input voltage	V _{SS} – 0.3	V _{DD} + 0.3	V
Ι _D	Instantaneous maximum current single pin limit (applies to all port pins)		25	mA
VDDA	Analog supply voltage	V _{DD} – 0.1	V _{DD} + 0.1	V

1. 60s lifetime - No restrictions, i.e. the part can switch.

10 hours lifetime - Device in reset, i.e. the part cannot switch.

5.3 General

5.3.1 Non-switching electrical specifications

5.3.1.1 Voltage and current operating requirements

Table 33. Voltage and current operating requirements

Symbol	Description	Min.	Max.	Unit	Notes
V_{DD}	Supply voltage	2.7	5.5	V	
V _{DDA}	Analog supply voltage	2.7	5.5	V	
V _{DD} – V _{DDA}	V _{DD} -to-V _{DDA} differential voltage	- 0.1	0.1	V	
V _{SS} – V _{SSA}	V _{SS} -to-V _{SSA} differential voltage	- 0.1	0.1	V	
IICIO	DC injection current — single pin			1	
	V _{IN} < V _{SS} - 0.3 V (Negative current injection)	- 3	_	mA	1
	$V_{IN} > V_{DD} + 0.3 V$ (Positive current injection)	_	+ 3	mA	
I _{ICcont}	Contiguous pin DC injection current — regional limit, includes sum of negative injection currents or sum of positive injection currents of 16 contiguous pins	- 25	+ 25	mA	
V _{ODPU}	Open drain pullup voltage level	VDD	VDD	V	2

1. All pins are internally clamped to V_{SS} and V_{DD} through ESD protection diodes. If V_{IN} is less than $V_{SS} - 0.3V$ or greater than $V_{DD} + 0.3V$, a current limiting resistor is required. The negative DC injection current limiting resistor is calculated as $R=(V_{SS} - 0.3V - V_{IN})/|I_{ICIO}|$. The positive injection current limiting resistor is calculated as $R=[V_{IN}-(V_{DD} + 0.3V)]/|I_{ICIO}|$. The actual resistor values should be an order of magnitude higher to tolerate transient voltages.

2. Open drain outputs must be pulled to $V_{\text{DD}}.$

5.3.1.2 DC electrical specifications at 3.3 V Range and 5.0 V Range

Table 34. DC electrical specifications

Symbol	Parameter	Value			Unit	Notes
		Min	Тур	Max		
V _{DD}	I/O Supply Voltage ¹ @ V _{DD} = 3.3 V	2.7	3.3	4	V	
	@ V _{DD} = 5.0 V	4	—	5.5	V	
Vih	Input Buffer High Voltage	0.7 × V _{DD}	_	V _{DD} + 0.3	V	

Table continues on the next page ...

	@ V _{DD} = 3.3 V					
	@ V _{DD} = 5.0 V	0.65 × V _{DD}	_	V _{DD} + 0.3	V	
Vil	Input Buffer Low Voltage	V _{SS} – 0.3	_	0.3 × V _{DD}	V	
	@ V _{DD} = 3.3 V					
	@ V _{DD} = 5.0 V	V _{SS} – 0.3		0.35 × V _{DD}	V	
V _{hys}	Input Buffer Hysteresis	0.06 × V _{DD}		_	V	
loh_5	Normal drive I/O current source capability measured when pad = $(V_{DD} - 0.8 V)$	2.8	_	-	mA	
	@ V _{DD} = 3.3 V					
	@ V _{DD} = 5.0 V	4.8		—	mA	
lol_5	Normal drive I/O current sink capability measured when pad = 0.8 V	2.4	_	_	mA	
	@ V _{DD} = 3.3 V					
	@ V _{DD} = 5.0 V	4.4	—	—	mA	
loh_20	High drive I/O current source capability measured when pad = (V_{DD} – 0.8 V), ²	10.8	_	-	mA	
	@ V _{DD} = 3.3 V					
	@ V _{DD} = 5.0 V	18.5	_	—	mA	
lol_20	High drive I/O current sink capability measured when pad = $0.8 \vee 4$	10.1	_	-	mA	
	@ V _{DD} = 3.3 V					
	@ V _{DD} = 5.0 V	18.5	_	—	mA ³	
l_leak	Hi-Z (Off state) leakage current (per pin)	_	_	300	nA	5,
V _{OH}	Output high voltage					7
	Normal drive pad (2.7 V \leq V _{DD} \leq 4.0 V, I _{OH} = - 2.8 mA)	V _{DD} – 0.8	_	_	V	
	Normal drive pad (4.0 V \leq V _{DD} \leq 5.5 V, I _{OH} = - 4.8 mA)	V _{DD} – 0.8	_	-	V	
	High drive pad (2.7 V \leq V _{DD} \leq 4.0 V, I _{OH} = - 10.8 mA)	V _{DD} – 0.8	_	-	V	
	High drive pad (4.0 V ≤ V _{DD} ≤ 5.5 V, I _{OH} = − 18.5 mA)	V _{DD} – 0.8	_	-	V	

Table 34. DC electrical specifications (continued)

Table continues on the next page...

I _{OHT}	Output high current total for all ports	_	_	100	mA		
V _{OL}	Output low voltage				·	7	
	Normal drive pad (2.7 V \leq V _{DD} \leq 4.0 V, I _{OH} = - 2.8 mA)	_	_	0.8	V		
	Normal drive pad (4.0 V \leq V _{DD} \leq 5.5 V, I _{OH} = - 4.8 mA)	_		0.8	V	-	
	High drive pad (2.7 V \leq V _{DD} \leq 4.0 V, I _{OH} = - 10.8 mA)	_	_	0.8	V	-	
	High drive pad (4.0 V \leq V _{DD} \leq 5.5 V, I _{OH} = - 18.5 mA)	_	_	0.8	V	-	
I _{OLT}	Output low current total for all ports	_		100	mA		
I _{IN}	Input leakage current (per pin) for full temperature range @ V _{DD} = 3.3 V						
	All pins other than high drive port pins	_	0.002	0.5	μA		
	High drive port pins	_	0.004	0.5	μA		
	Input leakage current (per pin) for full temperature range @ V _{DD} = 5.5 V						
	All pins other than high drive port pins	_	0.005	0.5	μΑ		
	High drive port pins	_	0.010	0.5	μA		
R _{PU}	Internal pull-up resistors @ V _{DD} = 3.3 V	20	_	65	kΩ	9	
	@ V _{DD} = 5.0 V	20	_	50	kΩ		
R _{PD}	Internal pull-down resistors @ V _{DD} = 3.3 V	20	_	65	kΩ	10	
	@ V _{DD} = 5.0 V	20		50	kΩ		

Table 34. DC electrical specifications (continued)

1. Max power supply ramp rate is 500 V/ms.

- 2. The value given is measured at high drive strength mode. For value at low drive strength mode see the loh_5 value given above.
- 3. The 20 mA I/O pin is capable of switching a 50 pF load at up to 40 MHz.
- 4. The value given is measured at high drive strength mode. For value at low drive strength mode see the lol_5 value given above.
- 5. Refers to the current that leaks into the core when the pad is in Hi-Z (Off state).
- 6. Maximum pin leakage current at the ambient temperature upper limit.
- 7. PTD0, PTD1, PTD15, PTD16, PTB4, PTB5, PTE0 and PTE1 I/O have both high drive and normal drive capability selected by the associated Portx_PCRn[DSE] control bit. All other GPIOs are normal drive only.
- 8. Refers to the pin leakage on the GPIOs when they are OFF.

9. Measured at V_{DD} supply voltage = V_{DD} min and input V = V_{SS} 10. Measured at V_{DD} supply voltage = V_{DD} min and input V = V_{DD}

5.3.1.3 Voltage regulator electrical characteristics

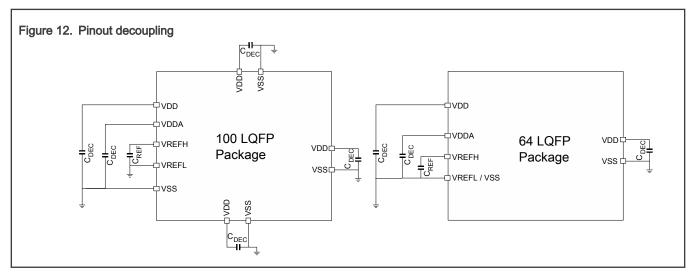


Table 35. Voltage regulator electrical characteristics

Symbol	Description	Min.	Тур.	Max.	Unit
C _{REF} ^{1,}	ADC reference high decoupling capacitance	_	100	—	nF
C _{DEC} ^{2, 3}	Recommended decoupling capacitance	_	100	—	nF

1. For improved ADC performance it is recommended to use 1 nF X7R/C0G and 10 nF X7R ceramics in parallel.

2. The capacitors should be placed as close as possible to the VREFH/VREFL pins or corresponding V_{DD}/V_{SS} pins.

3. The requirement and value of C_{DEC} will be decided by the device application requirement.

5.3.1.4 LVR, LVD and POR operating requirements

Table 36. \	V _{DD} supply LVR,	LVD and POR	operating requirements
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Symbol	Description	Min.	Тур.	Max.	Unit	Notes
VPOR	Rising and Falling V _{DD} POR detect voltage	1.1	1.572	2.0	V	
V _{LVRX}	LVRX falling threshold (RUN and STOP modes)	2.53	2.58	2.64	V	
V _{LVRX_HYST}	LVRX hysteresis	_	45	_	mV	
V _{LVRX_LP}	LVRX falling threshold (VLPS/VLPR modes)	1.97	2.12	2.44	V	
V _{LVRX_LP_HYST}	LVRX hysteresis (VLPS/VLPR modes)	_	40	_	mV	
V _{LVD}	Falling low-voltage detect threshold	2.8	2.88	3	V	
V _{LVD_HYST}	LVD hysteresis	_	50	_	mV	1

Table continues on the next page ...

V _{LVW}	Falling low-voltage warning threshold	4.19	4.31	4.5	V	
V _{LVW_HYST}	LVW hysteresis		68		mV	1
V _{BG}	Bandgap voltage reference	0.97	1.00	1.03	V	

Table 36. V_{DD} supply LVR, LVD and POR operating requirements (continued)

1. Rising threshold is the sum of falling threshold and hysteresis voltage.

5.3.1.5 Power mode transition operating behaviors

Table 37. Power mode transition operating behaviors

Description	System Clock	Core, Bus, Flash frequency (MHz)	Min.	Typ. ¹	Max. ²	Unit
STOP→RUN	FIRC	48, 24, 24	_	7.86	14.58	μs
STOP→RUN	FLL	72, 24, 24	_	8.13	15.4	μs
VLPS→RUN	FIRC	48, 24, 24	_	7.85	14.7	μs
VLPS→RUN	FLL	72, 24, 24	_	10.57	19.07	μs
RUN→HSRUN	FLL	72, 24, 24→96, 24, 24	_	4.03	6.85	μs
HSRUN→RUN	FLL	96, 24, 24→72, 24, 24	_	714	1165	ns
RUN→VLPR	FLL→SIRC	72, 24, 24→4, 1, 1	—	14.68	15.57	μs
VLPR→RUN	SIRC→FIRC	4, 1, 1→48, 24, 24	_	23.32	35.45	μs
VLPR→RUN	SIRC→FLL	4, 1, 1→72, 24, 24		26.86	38.71	μs
WAIT→RUN	FIRC	48, 24, 24	_	618	726	ns
WAIT→RUN	FLL	72, 24, 24	_	470	568	ns
VLPW→VLPR	SIRC	4, 1, 1		20.31	28.07	μs
VLPS→VLPR	SIRC	4, 1, 1	—	17.78	24.38	μs
VLPW→RUN	FIRC (reset value)	48, 24, 24 (reset value)	_	100.230	114.710	μs
tPOR ³	FIRC (reset value)	48, 24, 24 (reset value)	_	86.610	108.12	μs

1. Typical value is the average of values tested at Temperature = 25 °C and V_{DD} = 3.3 V.

2. Max value is mean + 6 × sigma of tested values at the worst case of ambient temperature range and V_{DD} 2.7 V to 5.5 V.

3. After a POR event, the amount of time from the point V_{DD} reaches the reference voltage 2.7 V to execution of the first instruction, across the operating temperature range of the chip.

5.3.1.6 Power consumption

Table 38 shows the power consumption targets for the device in various modes of operations.

NOTE

The maximum values stated in the table represent characterized results equivalent to the mean plus three times the standard deviation (mean + 3 sigma).

Specifications below only inculde power rails of the MCU (VDD, VDDA, and VREFH).

Table 38. P	Power consum	otion operatir	a behaviors
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Mode	Symbol	Clock Configura tion	Description	Temperat ure	Min	Тур	Max ¹	Unit
HSRUN I _{DD_HSRUN}	I _{DD_HSRUN}	LPFLL	Running CoreMark in Flash in Compute Operation mode. Core at 96 MHz, bus at	25 °C		12.97	13.26	mA
			24 MHz, flash at 24 MHz, VDD = 5 V	105 °C	_	13.63	14.09	
		LPFLL	Running CoreMark in Flash, all peripheral clock disabled. Core at 96	25 ℃	_	13.59	13.9	mA
			MHz, bus at 24 MHz, flash at 24 MHz, VDD = 5 V	105 ℃	_	14.29	14.77	
		LPFLL	Running CoreMark in Flash, all peripheral clock enabled. Core at 96	25 °C		17.04	17.42	mA
		MHz, bus at 24 MHz, flash at 24 MHz, VDD = 5 V	105 ℃	_	17.75	18.35		
		LPFLL	Running While (1) loop in Flash, all peripheral clock disabled. Core at 96	25 °C		10.2	10.43	mA
				105 ℃	_	10.84	11.2	
		LPFLL Running While (1) loop in Flash, all peripheral clock enabled. Core at 96	25 °C	_	13.65	13.96	mA	
		MHz, bus at 24 MHz, flash at 24 MHz, VDD = 5 V	105 ℃	_	14.33	14.81		
RUN	I _{DD_RUN} LPFLL Running CoreMark in Flash in Compute Operation mode.	I _{DD_RUN} LPFLL	25 °C	_	9.75	10	mA	
			Core at 72 MHz, bus at 24 MHz, flash at 24 MHz, VDD = 5 V	105 ℃	_	10.33	10.69	
		LPFLL	Running CoreMark in Flash all peripheral clock disabled.	25 ℃		10.12	10.38	mA
		Core at 72 MHz, bus at 24 MHz, flash at 24	105 °C	_	10.61	10.98		
		LPFLL	Running CoreMark in Flash, all peripheral clock enabled.	25 °C		12.1	12.41	mA
			Core at 72 MHz, bus at 24 MHz, flash at 24	105 °C	_	12.65	13.09	
		LPFLL	Running While (1) loop in Flash, all peripheral clock disabled.	25 ℃	_	7.94	8.15	mA
			penpheral clock disabled.	105 °C	_	8.47	8.76	

Table continues on the next page ...

Table 38.	Power consumption	operating	behaviors	(continued)
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			Core at 72 MHz, bus at 24 MHz, flash at 24 MHz, VDD = 5 V					
		LPFLL	Running While (1) loop in Flash all peripheral clock enabled.	25 ℃	_	10.31	10.58	mA
			Core at 72 MHz , bus at 24 MHz, flash at 24 MHz, VDD = 5 V	105 ℃	_	10.88	11.26	
		IRC48	Running CoreMark in Flash in Compute Operation mode.	25 ℃	_	7.71	7.85	mA
			Core at 48 MHz, bus at 24 MHz, flash at 24 MHz, VDD = 5 V	105 ℃	_	8.22	8.58	
		IRC48	Running CoreMark in Flash all peripheral clock disabled.	25 ℃	_	8.64	8.79	mA
			Core at 48 MHz, bus at 24 MHz, flash at 24 MHz, VDD = 5 V	105 ℃	_	9.13	9.53	
		IRC48	Running CoreMark in Flash, all peripheral clock enabled.	25 °C	_	10.4	10.58	mA
			Core at 48 MHz, bus at 24 MHz, flash at 24 MHz, VDD = 5 V	105 °C	_	10.9	11.38	
		IRC48	Running While (1) loop in Flash, all peripheral clock disabled.	25 °C	_	6.43	6.54	mA
			Core at 48 MHz, bus at 24 MHz, flash at 24 MHz, VDD = 5 V	105 °C	_	6.9	7.2	
		IRC48	Running While (1) loop in Flash, all peripheral clock enabled.	25 °C	—	8.2	8.35	mA
			Core at 48 MHz, bus at 24 MHz, flash at 24 MHz, VDD = 5 V	105 °C	_	8.67	9.05	
VLPR	I _{DD_VLPR}	IRC8M	Very Low Power Run Core Mark in Flash in Compute Operation mode.	25 °C	_	924	951	μA
			Core at 4 MHz, bus at1 MHz, flash at1 MHz, VDD = 5 V					
		IRC8M	Very Low Power Run Core Mark in Flash all peripheral clock disabled.	25 ℃	_	972	1001	
			Core at 4 MHz, bus at1 MHz, flash at1 MHz, VDD = 5 V					
		IRC8M	Very Low Power Run Core Mark in Flash all peripheral clock enabled.	25 ℃	_	1092	1124	
			Core at 4 MHz, bus at1 MHz, flash at1 MHz, VDD = 5 V					

Table continues on the next page...

		IRC8M	Very Low Power Run While (1) loop in Flash all peripheral clock disabled.	25 °C	_	702	723	
			Core at 4 MHz, bus at1 MHz, flash at1 MHz, VDD = 5 V					
		IRC8M	Very Low Power Run While (1) loop in Flash all peripheral clock enabled.	25 ℃		822	846	
			Core at 4 MHz, bus at 1 MHz, flash at1 MHz, VDD = 5 V					
		IRC2M	Very Low Power Run While (1) loop in Flash all peripheral clock disabled.	25 ℃		577	600	
			Core at 2 MHz, bus at 1 MHz, flash at1 MHz, VDD = 5 V					
		IRC2M	Very Low Power Run While (1) loop in Flash all peripheral clock enabled.	25 ℃		648	674	
			Core at 2 MHz, bus at 1 MHz, flash at 1 MHz, VDD = 5 V					
WAIT	I _{DD_WAIT}	LPFLL	core disabled, system at 72 MHz, bus at 24 MHz, flash disabled (flash doze enabled), VDD = 5 V, all peripheral clocks disabled	25 °C		5.88	6	mA
		IRC48M	core disabled, system at 48 MHz, bus at 24 MHz, flash disabled (flash doze enabled), VDD = 5 V, all peripheral clocks disabled	25 °C		4.8	4.89	-
VLPW	I _{DD_VLPW}	IRC8M	Very Low Power Wait current, core disabled system at 4 MHz, bus and flash at 1 MHz, all peripheral clocks disabled, VDD = 5 V	25 °C		642	665	μA
		IRC2M	Very Low Power Wait current, core disabled system at 2 MHz, bus and flash at 1 MHz, all peripheral clocks disabled, VDD = 5 V	25 °C	_	547	572	
STOP	I _{DD_STOP}	-	Stop mode current, VDD = 5 V, bias enabled ² , clock bias disabled ³ , all	25 °C and below	_	26	40	μA
			peripheral clocks disabled	50 °C	_	30.1	45.9	
				85 °C	_	59.7	91	-
				105 °C	_	104.1	158.7	1

Table 38. Power consumption operating behaviors (continued)

Table continues on the next page...

STOP I _{DD_STOP}	I _{DD_STOP}	DD_STOP - Stop mode current, VDD = 5V, bias enabled ² , clock bias disabled ³ , all peripheral clocks disabled	25 °C and below		22.7	35	μA	
				50 ℃	_	28	42.7	
				85 ℃	_	56.8	86.6	
				105 ℃	_	101	153.9	
VLPS I _{DD_VLPS}	I _{DD_VLPS}	- Very Low Power Stop current, VDD = 5 V, bias enable4, clock bias enabled ³ , all peripheral clocks disabled	25 °C and below		26	36.9	μA	
		50 ℃	_	31.2	47.5			
				85 °C	_	59.9	91.2	
				105 ℃	_	102.5	156.1	
VLPS	IDD_VLPS - Very Low Power Stop current, VDD = 5 V, bias enable4 ² , clock bias disabled ³ , all peripheral clocks disabled	V, bias enable4 ² , clock bias disabled ³ , all	25 °C and below		22.7	32.2	μA	
		50 °C	_	27.9	42.5			
				85 ℃	_	56.8	86.5	
				105 ℃	—	99.7	151.9	

Table 38. Power consumption operating behaviors (continued)

1. These values are based on characterization of typical samples, but not covered by test limits in production.

2. PMC_REGSC[BIASEN] is the control bit to enable or disable bias under low power mode.

3. PMC_REGSC[CLKBIASDIS] is the control bit to enable or disable clock bias under STOP / VLPS mode.

NOTE CoreMark benchmark compiled using IAR 9.40 with optimization level high, optimized for balanced.

5.3.1.6.1 Low power mode peripheral current adder — typical value

Table 39. Low power mode peripheral current adder - typical value

Symbol	Description	Typical
I _{LPTMR}	LPTMR peripheral adder measured by placing the device in VLPS mode with LPTMR enabled using LPO. Includes LPO power consumption.	366 nA
I _{CMP}	CMP peripheral adder measured by placing the device in VLPS mode with CMP enabled using the 8-bit DAC and a single external input for compare. 8-bit DAC enabled with half VDDA voltage, low speed mode. Includes 8-bit DAC power consumption.	16 µA
I _{LPUART}	LPUART peripheral adder measured by placing the device in VLPS mode with selected clock source waiting for RX data at 115200 baud rate. Includes selected clock source power consumption (SIRC 8 MHz).	79 µA

Table continues on the next page...

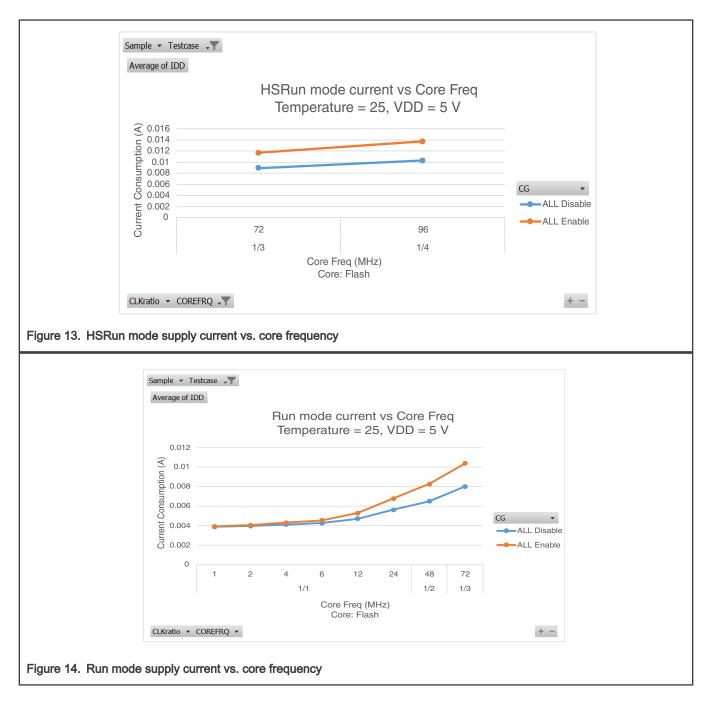
I _{FTM}	FTM peripheral adder measured by placing the device in VLPW mode with selected clock source, outputting the edge aligned PWM of 100 Hz frequency.	45 µA
I _{ADC}	ADC peripheral adder combining the measured values at VDD and VDDA by placing the device in VLPS mode. ADC is configured for low power mode using SIRC clock source, 8-bit resolution and continuous conversions.	591 µA
I _{LPI2C}	LPI2C peripheral adder measured by placing the device in VLPS mode with selected clock source sending START and Slave address, waiting for RX data. Includes the DMA power consumption.	179 µA
I _{LPIT}	LPIT peripheral adder measured by placing the device in VLPS mode with internal SIRC 8 MHz enabled in Stop mode. Includes selected clock source power consumption.	18 µA
I _{LPSPI}	LPSPI peripheral adder measured by placing the device in VLPS mode with selected clock source, output data on SOUT pin with SCK 500 kbit/s. Includes the DMA power consumption.	565 µA
I _{TSI}	TSI self-cap mode: TSI peripheral adder measured by placing the device in VLPS mode, switching frequency of TSI self-cap mode is configured to 1 MHz. TSI self-cap mode scans continuously with a 1 ms time period.	184.8 µA
	TSI mutual-cap mode: TSI peripheral adder measured by placing the device in VLPS mode, switching frequency of TSI mutual-cap mode is configured to 1 MHz. TSI mutual-cap mode scans continuously with a 1 ms time period.	285.6 μA
I _{SCI}	SCI peripheral adder measured by placing the device in wait mode with bus clock waiting for RX data at 115200 baud rate.	36.6 µA
I _{RTC}	RTC peripheral adder measured by placing the device in VLPS mode with LPO 1 kHz enabled by means of the RTC_CR[LPOS] bit and the RTC counter enabled. It includes LPO power consumption.	3.07 µA

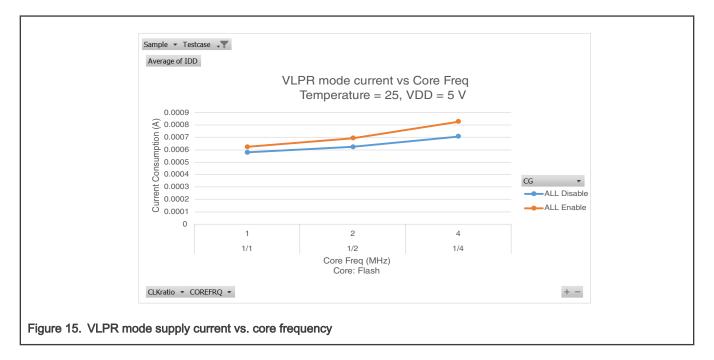
Table 39. Low power mode peripheral current adder — typical value (continued)

5.3.1.6.2 Diagram: Typical IDD_HSRUN, IDD_RUN, IDD_VLPR operating behavior

The following data are measured under these conditions:

- SCG in SOSC for HSRun, Run, and VLPR modes
- No GPIOs toggled
- Code execution from flash with cache enabled
- For the ALL Disable curve, all peripheral clocks are disabled except FTFE
- Running while (1) loop in Flash





5.3.1.7 EMC performance

Electromagnetic compatibility (EMC) performance is highly dependent on the environment in which the MCU resides. Board design and layout, circuit topology choices, location and characteristics of external components, and MCU software operation play a significant role in the EMC performance. The system designer can consult the following applications notes, available on http://www.nxp.com for advice and guidance specifically targeted at optimizing EMC performance.

- · AN2321: Designing for Board Level Electromagnetic Compatibility
- · AN1050: Designing for Electromagnetic Compatibility (EMC) with HCMOS Microcontrollers
- · AN1263: Designing for Electromagnetic Compatibility with Single-Chip Microcontrollers
- · AN2764: Improving the Transient Immunity Performance of Microcontroller- Based Applications
- · AN1259: System Design and Layout Techniques for Noise Reduction in MCU- Based Systems

5.3.1.7.1 EMC radiated emissions operating behaviors

EMC measurements to IC-level IEC standards are available from NXP on request.

5.3.1.7.2 Designing with radiated emissions in mind

To find application notes that provide guidance on designing your system to minimize interference from radiated emissions.

- 1. Go to http://www.nxp.com.
- 2. Perform a keyword search for "EMC design".
- 3. Select the "Documents" category and find the application notes.

5.3.1.8 Capacitance attributes

 Table 40.
 Capacitance attributes

Symbol Description Min. Max. Un	t
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Table continues on the next page...

Table 40. Capacitance attributes (continued)

C _{IN_A}	Input capacitance: analog pins	_	7	pF
C _{IN_D}	Input capacitance: digital pins	_	7	pF

NOTE

Please see External Oscillator electrical specifications for EXTAL/XTAL pins.

5.3.2 Switching specifications

5.3.2.1 Device clock specifications

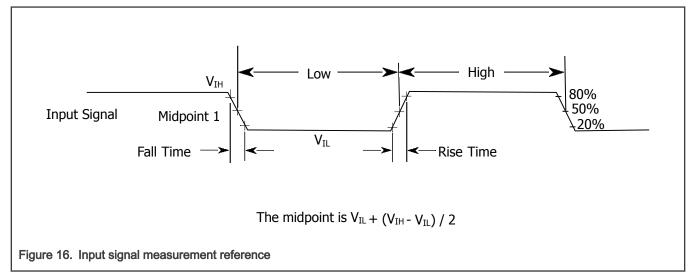
Table 41. Device clock specifications

Symbol	Description	Min.	Max.	Unit	Notes
	HSRUN mode				
f _{SYS}	System and core clock	_	96	MHz	
f _{BUS}	Bus clock		24	MHz	
f _{FLASH}	Flash clock		24	MHz	
	Normal run mode	9	1		-
f _{SYS}	System and core clock		72	MHz	
f _{BUS}	Bus clock		24	MHz	
f _{FLASH}	Flash clock		24	MHz	
f _{LPTMR}	LPTMR clock	_	48	MHz	
	VLPR / VLPW mod	e ¹			·
f _{SYS}	System and core clock	—	4	MHz	
f _{BUS}	Bus clock	—	1	MHz	
f _{FLASH}	Flash clock		1	MHz	
f _{ERCLK}	External reference clock		16	MHz	
f _{LPTMR}	LPTMR clock		13	MHz	

1. The frequency limitations in VLPR / VLPW mode here override any frequency specification listed in the timing specification for any other module.

5.3.2.2 AC electrical characteristics

Unless otherwise specified, propagation delays are measured from the 50% to the 50% point, and rise and fall times are measured at the 20% and 80% points, as shown in the following figure.



All digital I/O switching characteristics, unless otherwise specified, assume that the output pins have the following characteristics.

- C_L = 30 pF loads
- Normal drive strength

5.3.2.3 General AC specifications

These general purpose specifications apply to all signals configured for GPIO, LPUART, SCI, and timers.

Table 42. General switching specifications

Symbol	Description	Min.	Max.	Unit	Notes
	GPIO pin interrupt pulse width (digital glitch filter disabled) — Synchronous path	1.5		Bus clock cycles	1, 2
	External RESET and NMI pin interrupt pulse width — Asynchronous path	100		ns	3
	GPIO pin interrupt pulse width (digital glitch filter disabled, passive filter disabled) — Asynchronous path	50		ns	4

1. This is the minimum pulse width that is guaranteed to pass through the pin synchronization circuitry. Shorter pulses may or may not be recognized. In Stop and VLPS modes, the synchronizer is bypassed so shorter pulses can be recognized in that case.

2. The greater of synchronous and asynchronous timing must be met.

3. These pins have a passive filter enabled on the inputs. This is the shortest pulse width that is guaranteed to be recognized.

4. These pins do not have a passive filter on the inputs. This is the shortest pulse width that is guaranteed to be recognized.

5.3.2.4 AC specifications at 3.3 V range

Table 43. Supply voltage range

Characteristic	Symbol	Min	Тур	Max	Unit
I/O Supply Voltage	Vdd ¹	2.7		4	V

1. Max power supply ramp rate is 500 V/ms.

Table 44. Functional pad AC specifications

Name	Prop Delay (ns) ¹	Rise/Fall Edge (ns) ²		Drive Load (pF)
	Мах	Min	Мах	
Normal drive I/O pad	17.5	5	17	25
	28	9	32	50
High drive I/O pad	19	5	17	25
CMOS Input ³	26	9	33	50
	4	1.2	3	0.5

1. Propagation delay measured from 50% of core side input to 50% of the output.

2. Edges measured using 20% and 80% of the VDD supply.

3. Input slope = 2 ns.

NOTE All measurements were taken accounting for 150 mV drop across VDD and VSS.

5.3.2.5 AC specifications at 5 V range

Table 45. I/O supply voltage range

Characteristic	Symbol	Min	Тур	Max	Unit
I/O Supply Voltage	Vdd ¹	4		5.5	V

1. Max power supply ramp rate is 500 V/ms

Table 46. Functional pad AC specifications

Name	Prop Delay (ns) ¹	Rise/Fall Edge (ns) ²		Drive Load (pF)
	Max	Min	Мах	
Normal drive I/O pad	12	3.6	10	25
	18	8	17	50
High drive I/O pad	13	3.6	10	25
CMOS Input ³	19	8	19	50
	3	1.2	2.8	0.5

1. As measured from 50% of core side input to 50% of the output.

2. Edges measured using 20% and 80% of the VDD supply.

3. Input slope = 2 ns.

NOTE

All measurements were taken accounting for 150 mV drop across VDD and VSS.

5.3.3 Thermal specifications

5.3.3.1 Thermal operating requirements

Table 47. Thermal operating requirements

Symbol	Description	Min.	Max.	Unit	Notes
TJ	Die junction temperature	-40	125	°C	
T _A	Ambient temperature	-40	105	°C	1

1. Maximum T_A can be exceeded only if the user ensures that T_J does not exceed maximum T_J . The simplest method to determine T_J is: $T_J = T_A + R_{\theta JA} \times$ chip power dissipation.

5.3.3.2 Thermal attributes

5.3.3.2.1 Description

The tables in the following sections describe the thermal characteristics of the device.

NOTE
Junction temperature is a function of die size, on-chip power dissipation, package thermal resistance, mounting
side (board) temperature, ambient temperature, air flow, power dissipation or other components on the board, and
board thermal resistance.

5.3.3.2.2 Thermal characteristics for the 100-pin LQFP package

Table 48.	Thermal character	ristics for the	100-pin LQFF	P package
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Rating	Board Type ¹	Symbol	Value	Unit
Junction to Ambient Thermal Resistance	JESD51-7, 2s2p	R _{θJA}	47	°C/W
Junction-to-Top of Package Thermal Characterization Parameter ²	JESD51-7, 2s2p	Ψ_{JT}	0.6	°C/W

1. Thermal test board meets JEDEC specification for this package (JESD51-7).

 Determined in accordance to JEDEC JESD51-2A natural convection environment. Thermal resistance data in this report is solely for a thermal performance comparison of one package to another in a standardized specified environment. It is not meant to predict the performance of a package in an application-specific environment.

5.3.3.2.3 Thermal characteristics for the 64-pin LQFP package

Rating	Board Type ¹	Symbol	Value	Unit
Junction to Ambient Thermal Resistance	JESD51-7, 2s2p	R _{θJA}	52	°C/W

Table continues on the next page...

Junction-to-Top of Package Thermal Characterization Parameter ²	JESD51-7, 2s2p	Ψ_{JT}	3	°C/W
Junction to Case Thermal Resistance ³	JESD51-7, 1s	R _{eJC}	20	°C/W

Table 49. Thermal characteristics for the 64-pin LQFP package (continued)

1. Thermal test board meets JEDEC specification for this package (JESD51-7).

 Determined in accordance to JEDEC JESD51-2A natural convection environment. Thermal resistance data in this report is solely for a thermal performance comparison of one package to another in a standardized specified environment. It is not meant to predict the performance of a package in an application-specific environment.

3. Junction-to-Case thermal resistance determined using an isothermal cold plate. Case temperature refers to the mold surface temperature at the package top side dead centre.

5.3.3.2.4 General notes for specifications at maximum junction temperature

An estimation of the chip junction temperature, T_J , can be obtained from this equation: $T_J = T_A + (R_{\theta JA} \times P_D)$

where:

- T_A = ambient temperature for the package (°C)
- R_{0JA} = junction to ambient thermal resistance (°C/W)
- P_D = power dissipation in the package (W)

The junction to ambient thermal resistance is an industry standard value that provides a quick and easy estimation of thermal performance. Unfortunately, there are two values in common usage: the value determined on a single layer board and the value obtained on a board with two planes. For packages such as the PBGA, these values can be different by a factor of two. Which value is closer to the application depends on the power dissipated by other components on the board. The value obtained on a single layer board is appropriate for the tightly packed printed circuit board. The value obtained on the board with the internal planes is usually appropriate if the board has low power dissipation and the components are well separated.

When a heat sink is used, the thermal resistance is expressed in the following equation as the sum of a junction-to-case thermal resistance and a case-to-ambient thermal resistance:

 $R_{\theta JA} = R_{\theta JC} + R_{\theta CA}$

where:

- R_{0JA} = junction to ambient thermal resistance (°C/W)
- R_{0JC} = junction to case thermal resistance (°C/W)
- R_{0CA} = case to ambient thermal resistance (°C/W)

 $R_{\theta JC}$ is device related and cannot be influenced by the user. The user controls the thermal environment to change the case to ambient thermal resistance, $R_{\theta CA}$. For instance, the user can change the size of the heat sink, the air flow around the device, the interface material, the mounting arrangement on printed circuit board, or change the thermal dissipation on the printed circuit board surrounding the device.

To determine the junction temperature of the device in the application when heat sinks are not used, the Thermal Characterization Parameter (Ψ_{JT}) can be used to determine the junction temperature with a measurement of the temperature at the top center of the package case using this equation:

 $T_J = T_T + (\Psi_{JT} \times P_D)$

where:

- T_T = thermocouple temperature on top of the package (°C)
- Ψ_{JT} = thermal characterization parameter (°C/W)

• P_D = power dissipation in the package (W)

The thermal characterization parameter is measured per JESD51-2 specification using a 40 gauge type T thermocouple epoxied to the top center of the package case. The thermocouple should be positioned so that the thermocouple junction rests on the package. A small amount of epoxy is placed over the thermocouple junction and over about 1 mm of wire extending from the junction. The thermocouple wire is placed flat against the package case to avoid measurement errors caused by cooling effects of the thermocouple wire.

5.4 Peripheral operating requirements and behaviors

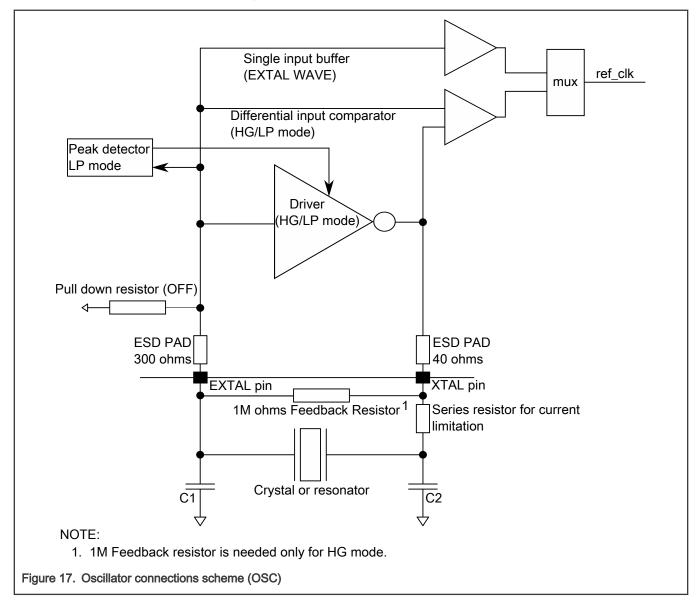
5.4.1 System modules

There are no specifications necessary for the device's system modules.

5.4.2 Clock interface modules

5.4.2.1 Oscillator electrical specifications

5.4.2.1.1 External Oscillator electrical specifications



NOTE

Data values in the following "External Oscillator electrical specifications" tables are from simulation.

Table 50. External Oscillator electrical specifications (OSC)

Symbol	Description	Min.	Тур.	Max.	Unit	Notes
V _{DD}	Supply voltage	2.7		5.5	V	
IDDOSC	Supply current — low-gain mode (low-power mode)					
	4 MHz	_	200	_	μA	

Table continues on the next page ...

	8 MHz	_	300	-	μA
	16 MHz	_	1.2	_	mA
	24 MHz	_	1.6	_	mA
	32 MHz	_	2	_	mA
	40 MHz	_	2.6	_	mA
DDOSC	Supply current — high-gain mode (HGO=1)				-
	32 kHz	_	25	_	μA
	4 MHz	_	1	_	mA
	8 MHz	_	1.2	_	mA
	16 MHz	_	3.5	_	mA
	24 MHz		5		mA
	32 MHz	_	5.5	_	mA
	40 MHz	_	6	_	mA
mXOSC	Fast external crystal oscillator transconductance		L		_
	SCG_SOSCCFG[RANGE] = 01b for Low Frequency Range, High Gain (32 kHz)	15		45	μA / V
	SCG_SOSCCFG[RANGE] = 10b for Medium Frequency Range (4-8 MHz)	2.2		9.7	mA / V
	SCG_SOSCCFG[RANGE] = 11b for High Frequency Range (8-40 MHz)	16	_	37	mA / V
V _{IH}	Input high voltage — EXTAL pin in external clock mode	1.75	_	V _{DD}	V
V _{IL}	Input low voltage — EXTAL pin in external clock mode	V _{SS}	_	1.20	V
C ₁	EXTAL load capacitance	_	_	_	
C ₂	XTAL load capacitance	_	_	_	
R _F	Feedback resistor	1			
	Low-frequency, high-gain mode (32 kHz)	_	10	_	MΩ

 Table 50. External Oscillator electrical specifications (OSC) (continued)

Table continues on the next page...

	Medium/high-frequency, low-gain mode (low-power mode) (4-8 MHz, 8-40 MHz)				MΩ	
	Medium/high-frequency, high-gain mode (4-8 MHz, 8-40 MHz)	_	1	_	MΩ	
R_S	Series resistor			1		
	Low-frequency, high-gain mode (32 kHz)	_	200		kΩ	
	Medium/high-frequency, low-gain mode (low-power mode) (4-8 MHz, 8-40 MHz)	_	0	_	kΩ	
	Medium/high-frequency, high-gain mode (4-8 MHz, 8-40 MHz)	_	0	_	kΩ	
Vpp	Peak-to-peak amplitude of oscillation (oscillator mod	de)				4
	Low-frequency, high-gain mode	_	3.3	_	V	
	Medium/high-frequency, low-gain mode	_	1.0	_	V	
	Medium/high-frequency, high-gain mode	_	3.3		V	

Table 50. External Oscillator electrical specifications (OSC) (continued)

1. Measured at V_{DD} = 5 V, Temperature = 25 °C. The current consumption is according to the crystal or resonator, loading capacitance.

2. C1 and C2 must be provided by external capacitors and their load capacitance depends on the crystal or resonator manufacturers' recommendation. Please check the crystal datasheet for the recommended values. And also consider the parasitic capacitance of package and board.

- 3. When low power mode is selected, R_F is integrated and must not be attached externally.
- 4. The EXTAL and XTAL pins should only be connected to required oscillator components and must not be connected to any other devices.

5.4.2.1.2 External Oscillator electrical specifications

Table 51.	External Oscillator	^r frequency	specifications	(OSC)
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Symbol	Description	Min.	Тур.	Max.	Unit	Notes
f _{osc_lo}	Oscillator crystal or resonator frequency — Low Frequency, High Gain Mode	32		40	kHz	
f _{osc_me}	Oscillator crystal or resonator frequency — Medium Frequency	4	_	8	MHz	
f _{osc_hi}	Oscillator crystal or resonator frequency — High Frequency	8		40		
t _{dc_extal}	Input clock duty cycle (external clock mode)	40	50	60	%	
f _{ec_extal}	Input clock frequency (external clock mode)	_	_	50	MHz	

Table continues on the next page ...

t .	Crystal startup time — 32 kHz Low Frequency,		500		ms	1
t _{cst}	High-Gain Mode		500	_	1115	
	Crystal startup time — 8 MHz Medium Frequency, Low-Power Mode	_	1.5	_		
	Crystal startup time — 8 MHz Medium Frequency, High-Gain Mode		2.5			
	Crystal startup time — 40 MHz High Frequency, Low-Power Mode		2			
	Crystal startup time — 40 MHz High Frequency, High-Gain Mode	_	2.5			

Table 51. External Oscillator frequency specifications (OSC) (continued)

1. The start-up measured after 4096 cycles. Proper PC board layout procedures must be followed to achieve specifications.

5.4.2.2 System Clock Generation (SCG) specifications

5.4.2.2.1 Fast internal RC Oscillator (FIRC) electrical specifications

Table 52. Fast internal RC Oscillator (FIRC) electrical specifications

Symbol	Parameter		Value		Unit
		Min.	Тур.	Max.	
F _{FIRC}	Fast internal reference frequency		48	_	MHz
I _{VDD}	Supply current	_	400	500	μA
F _{Untrimmed}	IRC frequency (untrimmed)	F _{IRC} × (1-0.3)		F _{IRC} × (1+0.3)	MHz
ΔF _{OL}	Open loop total deviation of IRC frequency over voltage and temperature ¹			1	
	Regulator enable		±0.5	±1	%F _{FIRC}
T _{Startup}	Startup time		_	3	µs²
T _{JIT}	Period jitter (RMS)	_	35	150	ps

1. The limit is respected across process, voltage and full temperature range.

2. Startup time is defined as the time between clock enablement and clock availability for system use.

5.4.2.2.2 Slow internal RC oscillator (SIRC) electrical specifications

Table 53. Slow internal RC oscillator (SIRC) electrical specifications

	Unit		Value		Parameter	Symbol
Min. Typ. Max		Max.	Тур.	Min.		

Table continues on the next page...

F _{SIRC}	Slow internal reference frequency	_	2 8	_	MHz
I _{VDD}	Supply current	_	23	_	μA
F _{Untrimmed}	IRC frequency (untrimmed)	_	_	_	MHz
ΔF _{OL}	Open loop total deviation of IRC frequency over voltage and temperature ¹				
	Regulator enable	_	_	±3	%F _{SIRC}
T _{Startup}	Startup time	_	6	_	μs ²

Table 53. Slow internal RC oscillator (SIRC) electrical specifications (continued)

1. The limit is respected across process, voltage and full temperature range.

2. Startup time is defined as the time between clock enablement and clock availability for system use.

5.4.2.2.3 Low Power Oscillator (LPO) electrical specifications

Table 54. Low Power Oscillator	(LPO) electrical specifications
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Symbol	Parameter	Min.	Тур.	Max.	Unit
F _{LPO}	F _{LPO} Internal low power oscillator frequency		128	139	kHz
I _{LPO}	Current consumption	1	3	7	μA
T _{startup}	Startup Time			20	μs

5.4.2.2.4 LPFLL electrical specifications

Toble 55		alastrias	specifications
i able 55.	LPTLL	electrical	specifications

Symbol	Parameter	Min.	Тур.	Max.	Unit
l _{avg}	Power consumption	_	250	_	μA
T _{start}	Start-up time	_	3.6	_	μs
ΔF _{ol}	Frequency accuracy over temperature and voltage in open loop after process trimmed	-10		10	%
ΔF _{cl}	Frequency accuracy in closed loop	-1 ¹	_	1 ¹	%

1. ΔF_{cl} is dependent on reference clock accuracy. For example, if locked to crystal oscillator, ΔF_{cl} is typically limited by trimming ability of the module itself; if locked to other clock source which has 3% accuracy, then ΔF_{cl} can only be ±3%.

5.4.3 Memories and memory interfaces

5.4.3.1 Flash memory module (FTFE) electrical specifications

This section describes the electrical characteristics of the flash memory module (FTFE).

5.4.3.1.1 Flash timing specifications - program and erase

The following specifications represent the amount of time the internal charge pumps are active and do not include command overhead.

Table 56.	NVM	program/erase	timing	specifications
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Symbol	Description	Min.	Тур.	Max.	Unit	Notes
t _{hvpgm8}	vpgm8 Program Phrase high-voltage time		7.5	18	μs	—
t _{hversscr}	cr Erase Flash Sector high-voltage time		13	113	ms	1
t _{hversblk512k}	Erase Flash Block high-voltage time for 512 KB		416	3616	ms	1

1. Maximum time based on expectations at cycling end-of-life.

5.4.3.1.2 Flash timing specifications --- command

Table 57. Flash command timing specifications

Symbol	Description	Min.	Тур.	Max.	Unit	Notes
t _{rd1blk512k}	Read 1s Block execution time • 512 KB program flash	_	_	1.8	ms	_
t _{rd1sec2k}	Read 1s Section execution time (2 KB flash)	_	_	75	μs	1
t _{pgmchk}	Program Check execution time	_	_	95	μs	1
t _{rdrsrc}	Read Resource execution time	_	_	40	μs	1
t _{pgm8}	Program Phrase execution time	_	90	150	μs	
t _{ersblk512k}	Erase Flash Block execution time • 512 KB program flash	_	435	3700	ms	2
t _{ersscr}	Erase Flash Sector execution time	_	15	115	ms	2
t _{pgmsec1k}	Program Section execution time (1 KB flash)	_	5	_	ms	_
t _{rd1allx}	Read 1s All Blocks execution time	_	_	2.2	ms	_
t _{rdonce}	Read Once execution time	_	_	30	μs	1
t _{pgmonce}	Program Once execution time	_	90	_	μs	_
t _{ersall}	Erase All Blocks execution time	_	500	4200	ms	2
t _{vfykey}	Verify Backdoor Access Key execution time	_	_	30	μs	1
t _{ersallu}	Erase All Blocks Unsecure execution time	_	500	4200	ms	2

1. Assumes 25 MHz or greater flash clock frequency.

2. Maximum times for erase parameters based on expectations at cycling end-of-life.

5.4.3.1.3 Flash high voltage current behaviors

Symbol	Description	Min.	Тур.	Max.	Unit
I _{DD_PGM}	Average current adder during high voltage flash programming operation	—	3.5	7.5	mA
I _{DD_ERS}	Average current adder during high voltage flash erase operation	_	1.5	4.0	mA

5.4.3.1.4 Reliability specifications

Table 59. NVM reliability specifications

Symbol	Description	Min.	Typ. ¹	Max.	Unit	Notes			
	Program Flash								
t _{nvmretp10k}	Data retention after up to 10 K cycles	5	50	—	years	—			
t _{nvmretp1k}	vmretp1k Data retention after up to 1 K cycles		100	_	years	—			
n _{nvmcycp}	Cycling endurance	10 K	50 K	_	cycles	2			

1. Typical data retention values are based on measured response accelerated at high temperature and derated to a constant 25 °C use profile. Engineering Bulletin EB618 does not apply to this technology. Typical endurance defined in Engineering Bulletin EB619.

2. Cycling endurance represents number of program/erase cycles at -40 °C \leq T_i \leq 125 °C.

5.4.4 Security and integrity modules

There are no specifications necessary for the device's security and integrity modules.

5.4.5 Analog

5.4.5.1 ADC electrical specifications

5.4.5.1.1 12-bit ADC operating conditions

Table 60. 12-bit ADC operating conditions

Symbol	Description	Conditions	Min.	Typ. ¹	Max.	Unit	Notes
V _{DDA}	Supply voltage	Absolute	2.7	—	5.5	V	
ΔV _{DDA}	Supply voltage	Delta to V _{DD} (V _{DD} – V _{DDA})	-100	0	+100	mV	
ΔV _{SSA}	Ground voltage	Delta to V _{SS} (V _{SS} – V _{SSA})	-100	0	+100	mV	2

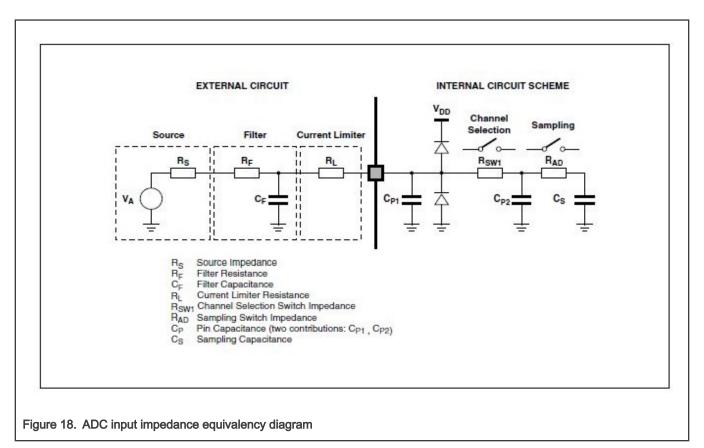
Table continues on the next page ...

V _{REFH}	ADC reference voltage high		2.5	V _{DDA}	V _{DDA} + 100m	V	
V _{REFL}	ADC reference voltage low		- 100	0	100	mV	3
V _{ADIN}	Input voltage		V _{REFL}	_	V _{REFH}	V	
R _S	Source impedance	f _{ADCK} < 4 MHz	_	_	5	kΩ	
R _{SW1}	Channel Selection Switch Impedance		_	0.5	1.2	kΩ	
R _{AD}	Sampling Switch Impedance		_	2	5	kΩ	
C _{P1}	Pin Capacitance		_	3	_	pF	
C _{P2}	Analog Bus Capacitance		_		5	pF	
C _S	Sampling capacitance		_	4	5	pF	
f _{ADCK}	ADC conversion clock frequency		2	40	50	MHz	4, 5
C _{rate}	ADC conversion rate	No ADC hardware averaging ⁶ Continuous conversions enabled, subsequent conversion time	20		1200	Ksps	7

Table 60. 12-bit ADC operating conditions (continued)

 Typical values assume V_{DDA} = 5 V, Temp = 25 °C, f_{ADCK} = 40 MHz, unless otherwise stated. Typical values are for reference only, and are not tested in production.

- 2. DC potential difference.
- 3. For packages without dedicated V_{REFH} and V_{REFL} pins, V_{REFH} is internally tied to V_{DDA}, and V_{REFL} is internally tied to VSSA.
- 4. Clock and compare cycle need to be set according to the guidelines in the device Reference Manual
- 5. ADC conversion will become less reliable above maximum frequency.
- 6. When using ADC hardware averaging, see the device *Reference Manual* to determine the most appropriate setting for AVGS.
- 7. Max ADC conversion rate of 1200 Ksps is with 10-bit mode



5.4.5.1.2 12-bit ADC electrical characteristics

NOTE

All the parameters in the table are given assuming system clock as the clocking source for ADC.

NOTE

For ADC signals adjacent to VDD/VSS or the XTAL pins some degradation in the ADC performance may be observed.

NOTE

All values guarantee the performance of the ADC for the multiple ADC input channel pins. When using the ADC to

monitor the internal analogue parameters, please assume minor degradation.

Table 61. 12-bit ADC characteristics ($V_{REFH} = V_{DDA}$, $V_{REFL} = V_{SSA}$)

Symbol	Description	Conditions ¹	Min.	Typ. ²	Max. ³	Unit	Notes
I _{DDA_ADC}	Supply current at 2.7 to 5.5 V			µA @ 5 V		μA	4
	Sample Time		275	_	Refer to the device's <i>Reference Manual</i>	ns	

Table continues on the next page...

TUE	Total unadjusted error at 2.7 to 5.5 V		_	±4.5	±6.11	LSB	6
DNL	Differential non- linearity at 2.7 to 5.5 V		_	±0.8	±1.07	LSB ⁵	6
INL	Integral non-linearity at 2.7 to 5.5 V		_	±1.4	±3.54	LSB ⁵	6
EFS	Full-scale error at 2.7 to 5.5 V		_	-2	-3.60	LSB ⁵	VADIN = V _{DDA} ⁶
EZS	Zero-scale error at 2.7 to 5.5 V			-2.7	-4.24	LSB ⁵	
EQ	Quantization error at 2.7 to 5.5 V		_	_	±0.5	LSB ⁵	
ENOB	Effective number of bits at 2.7 to 5.5 V		_	11.3	_	bits	7
SINAD	Signal-to-noise plus distortion at 2.7 to 5.5 V	See ENOB		70		dB	SINAD = 6.02 × ENOB + 1.76
E _{IL}	Input leakage error at 2.7 to 5.5 V		I _{In} × RAS			mV	I _{In} = leakage current (refer to the MCU's voltage and current operating ratings)
V _{TEMP_S}	Temp sensor slope at 2.7 to 5.5 V	Across the full temperature range of the device	1.492	1.564	1.636	mV/°C	8, 9
V _{TEMP25}	Temp sensor voltage at 2.7 to 5.5 V	25 °C	730	740.5	751	mV	8, 9

Table 61. 12-bit ADC characteristics (V_{REFH} = V_{DDA}, V_{REFL} = V_{SSA}) (continued)

1. All accuracy numbers assume the ADC is calibrated with $V_{REFH} = V_{DDA}$

2. Typical values assume V_{DDA} = 5.0 V, Temp = 25 °C, f_{ADCK} = 48 MHz unless otherwise stated.

3. These values are based on characterization but not covered by test limits in production.

4. The ADC supply current depends on the ADC conversion clock speed, conversion rate and ADC_CFG1[ADLPC] (low power). For lowest power operation, ADC_CFG1[ADLPC] must be set, the ADC_CFG2[ADHSC] bit must be clear with 1 MHz ADC conversion clock speed.

5. 1 LSB = $(V_{REFH} - V_{REFL})/2N$

6. ADC conversion clock < 16 MHz, Max hardware averaging (AVGE = %1, AVGS = %11)

- 7. Input data is 100 Hz sine wave. ADC conversion clock < 40 MHz.
- 8. ADC conversion clock < 3 MHz

9. The sensor must be calibrated to gain good accuracy, so as to provide good linearity, see also AN3031 for more detailed application information of the temperature sensor.

5.4.5.2 CMP with 8-bit DAC electrical specifications

Table 62.	Comparator wit	h 8-bit DAC electrica	specifications
-----------	----------------	-----------------------	----------------

Symbol	Description	Min.	Typ. ¹	Max.	Unit	
V _{DD}	Supply voltage	2.7	_	5.5	V	
I _{DDHS}	Supply current, High-speed mode		II		μA	
	within ambient temperature range —		145	200		
I _{DDLS}	Supply current, Low-speed mode ²		<u> </u>		μA	
	within ambient temperature range — 5		5	10		
VAIN	Analog input voltage	0	0 - V _{DDX} V _{DDX}		V	
V _{AIO}	Analog input offset voltage, High-speed mode				mV	
	within ambient temperature range	-25	±1	25		
V _{AIO}	Analog input offset voltage, Low-speed mode		· · ·		mV	
	within ambient temperature range	-40	±4	40		
t _{DHSB}	Propagation delay, High-speed mode		· · ·		ns	
	within ambient temperature range	_	30	200		
t _{DLSB}	Propagation delay, Low-speed mode ³		· · ·		μs	
	within ambient temperature range	_	0.5	2	_	
t _{DHSS}	Propagation delay, High-speed mode			ns		
	within ambient temperature range	- 70 400				
t _{DLSS}	Propagation delay, Low-speed mode ⁴		· · ·		μs	
	within ambient temperature range	_	1	5		
t _{IDHS}	Initialization delay, High-speed mode ³		· · · ·		μs	
	within ambient temperature range	_	1.5	3		
t _{IDLS}	Initialization delay, Low-speed mode ³				μs	
	within ambient temperature range	_	10	30		
V _{HYST0}	Analog comparator hysteresis, Hyst0 (V _{AIO})				mV	
	within ambient temperature range	_	0	_		

Table continues on the next page ...

M						
V _{HYST1}	Analog comparator hysteresis, Hyst1, High- speed mode			mV		
	within ambient temperature range		16	53		
	Analog comparator hysteresis, Hyst1, Low-speed mode		-			
	within ambient temperature range	_	11	30		
V _{HYST2}	Analog comparator hysteresis, Hyst2, High- speed mode				mV	
	within ambient temperature range	_	32	90		
	Analog comparator hysteresis, Hyst2, Low-speed mode					
	within ambient temperature range	_	22	53		
V _{HYST3}	Analog comparator hysteresis, Hyst3, High- speed mode			mV		
	within ambient temperature range	—	48	133		
	Analog comparator hysteresis, Hyst3, Low-speed mode					
	within ambient temperature range	—	33	80		
I _{DAC8b}	8-bit DAC current adder (enabled)	—	10	16	μA	
INL	8-bit DAC integral non-linearity	-0.6		0.5	LSB ⁵	
DNL	8-bit DAC differential non-linearity	-0.5	_	0.5	LSB	

Table 62. Comparator with 8-bit DAC electrical specifications (continued)

1. Typical values assumed at VDDA = 5.0 V, Temp = 25 °C, unless otherwise stated.

2. Difference at input > 200mV

3. Applied ± (100 mV + Hyst) around switch point

4. Applied \pm (30 mV + 2 × Hyst) around switch point

5. 1 LSB = $V_{reference}/256$

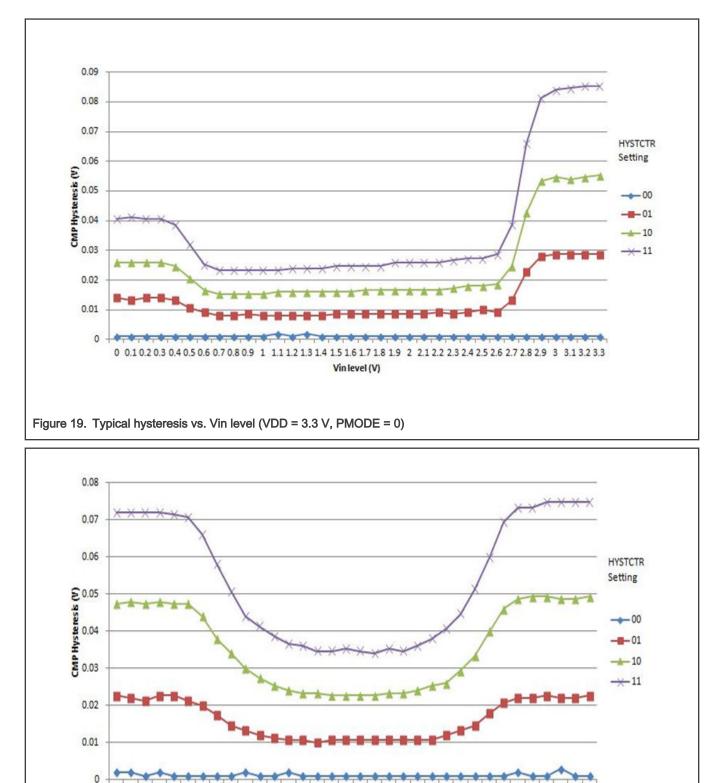
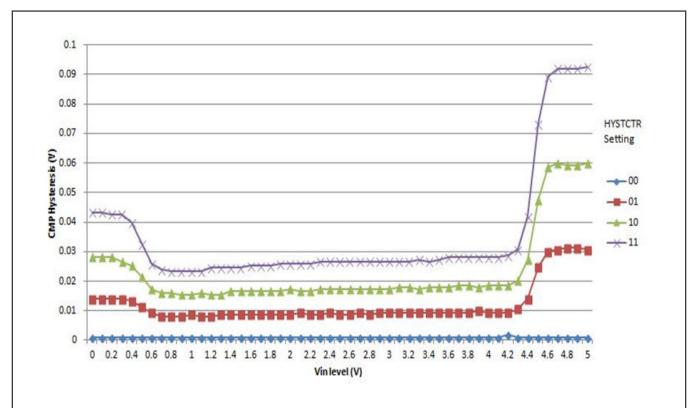
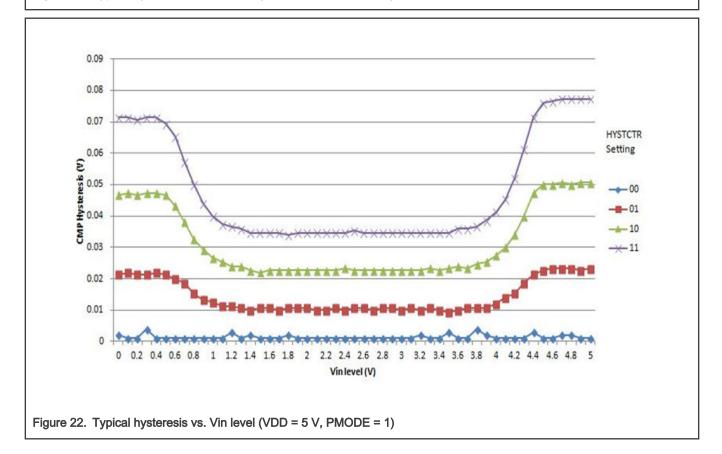


Figure 20. Typical hysteresis vs. Vin level (VDD = 3.3 V, PMODE = 1)

0 0.10.20.3 0.40.5 0.6 0.7 0.8 0.9 1 1.1 1.2 1.3 1.4 1.5 1.6 1.7 1.8 1.9 2 2.1 2.2 2.3 2.4 2.5 2.6 2.7 2.8 2.9 3 3.1 3.2 3.3 Vin level (V)







5.4.6 Communication interfaces

5.4.6.1 LPUART electrical specifications

Refer to General AC specifications for LPUART specifications.

5.4.6.2 LPSPI electrical specifications

The Low Power Serial Peripheral Interface (LPSPI) provides a synchronous serial bus with master and slave operations. Many of the transfer attributes are programmable.

The following tables provide timing characteristics for classic LPSPI timing modes.

All timing is shown with respect to 20% V_{DD} and 80% V_{DD} thresholds, unless noted, as well as input signal transitions of 3 ns and a 25 pF maximum load on all LPSPI pins.

Num.	Symbol	Description	Min.	Max.	Unit	Note
1	f _{SPSCK}	Frequency of SPSCK	f _{periph} /2048	f _{periph} /2	Hz	1
2	t _{SPSCK}	SPSCK period	2 x t _{periph}	2048 x	ns	2
				t _{periph}		
3	tLead	Enable lead time	1/2		t _{SPSCK}	_
4	tLag	Enable lag time	1/2	_	t _{SPSCK}	_
5	t _{WSPSCK}	Clock (SPSCK) high or low time	t _{periph} - 30	1024 x	ns	_
				t _{periph}		
6	t _{SU}	Data setup time (inputs)	18		ns	
7	t _{HI}	Data hold time (inputs)	0	_	ns	_
8	t _v	Data valid (after SPSCK edge)	_	15	ns	_
9	t _{HO}	Data hold time (outputs)	0	_	ns	_
10	t _{RI}	Rise time input	_	t _{periph} - 25	ns	_
	t _{FI}	Fall time input				
11	t _{RO}	Rise time output	_	25	ns	_
	t _{FO}	Fall time output				

Table 63. LPSPI master mode timing

1. f_{periph} is LPSPI peripheral functional clock. The maximum frequency of f_{SPSCK} cannot be exceed 25 MHz.

2. $t_{periph} = 1/fperiph$

High drive pin should be used for fast bit rate.

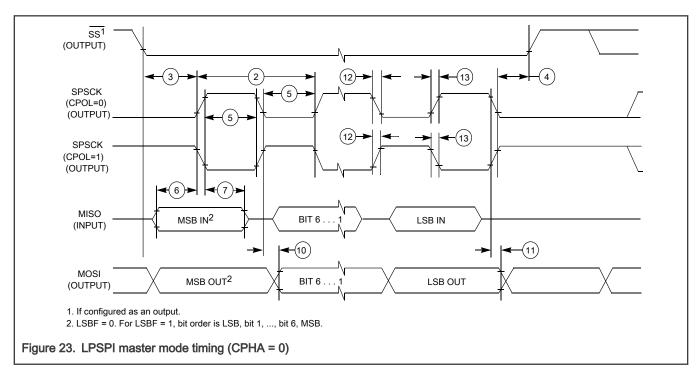
NOTE

When LPSPI transmitting data with using pins in Table 64, the maximum frequency of f_{SPSCK} can reach 48 MHz in HSRUN mode.

Table 64. Specifical pins can reach 48 MHz frequency

LPSPI pin	Pin name
LPSPI0	PTE0 / LPSPI0_SCK1
	PTE2 / LPSPI0_SOUT
	PTE6 / LPSPI0_PCS2
LPSPI1	PTD0 / LPSPI1_SCK ¹
	PTD2 / LPSPI1_SOUT
	PTD3 / LPSPI1_PSC0
	PTA16 / LPSPI1_PCS2

1. High drive pin



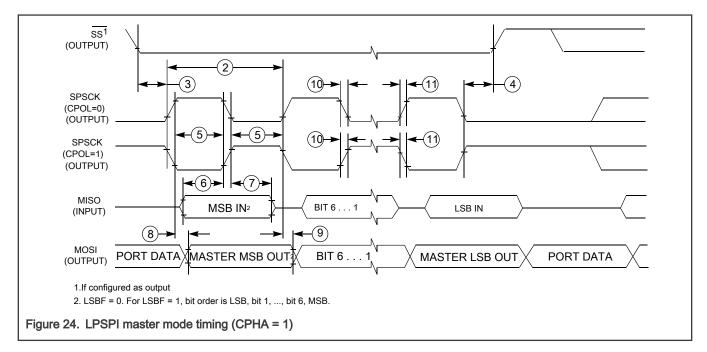


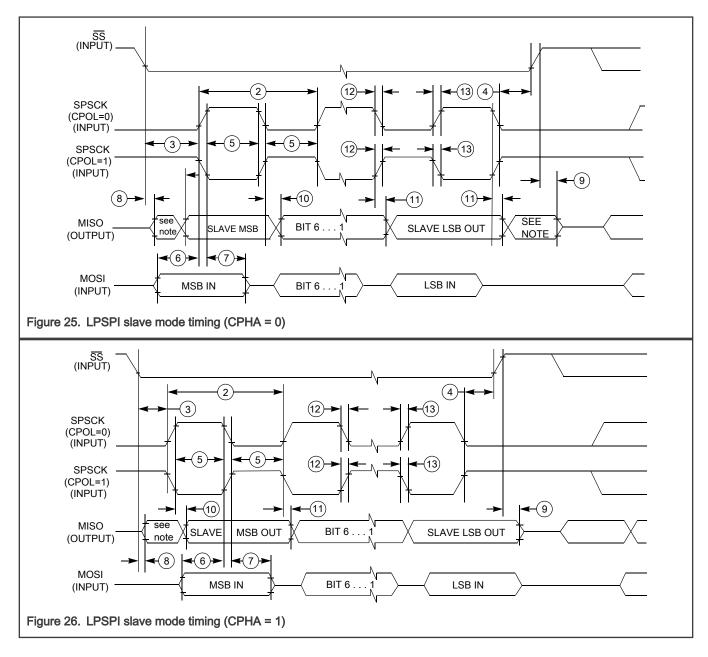
Table 65. LPSPI slave mode timing on slew rate enabled pads

Num.	Symbol	Description	Min.	Max.	Unit	Note
1	f _{SPSCK}	Frequency of SPSCK	0	f _{periph} /2	Hz	1
2	t _{SPSCK}	SPSCK period	2 x t _{periph}	_	ns	2
3	t _{Lead}	Enable lead time	1	_	t _{periph}	_
4	t _{Lag}	Enable lag time	1	_	t _{periph}	_
5	t _{WSPSCK}	Clock (SPSCK) high or low time	t _{periph} - 30	—	ns	_
6	t _{SU}	Data setup time (inputs)	2	_	ns	_
7	t _{HI}	Data hold time (inputs)	7	_	ns	_
8	t _a	Slave access time	_	t _{periph}	ns	3
9	t _{dis}	Slave MISO disable time	_	t _{periph}	ns	4
10	t _v	Data valid (after SPSCK edge)	_	122	ns	_
11	t _{HO}	Data hold time (outputs)	0	_	ns	_
12	t _{RI}	Rise time input	_	t _{periph} - 25	ns	_
	t _{FI}	Fall time input	1			
13	t _{RO}	Rise time output	_	36	ns	-
	t _{FO}	Fall time output				

f_{periph} = LPSPI peripheral functional clock. The maximum frequency of f_{SPSCk} cannot be exceed 25 MHz.
 t_{periph} = 1/f_{periph}

Time to data active from high-impedance state 3.

4. Hold time to high-impedance state



5.4.6.3 LPI2C

Table	66.	LPI2C	specifications
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Symbol	Description		Min.	Max.	Unit	Notes
f _{SCL}	SCL clock frequency	Standard mode (Sm)	0	100	kHz	1, 2, 3
		Fast mode (Fm)	0	400		
		Fast mode Plus (Fm+)	0	1000		
		Ultra Fast mode (UFm)	0	5000		
		High speed mode (Hs-mode)	0	3400		

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- 1. Hs-mode is only supported in slave mode.
- 2. The maximum SCL clock frequency in Fast mode with maximum bus loading (400pF) can only be achieved with appropriate pull-up devices on the bus when using the high or normal drive pins across the full voltage range. The maximum SCL clock frequency in Fast mode Plus can support maximum bus loading (400pF) with appropriate pull-up devices when using the high drive pins. The maximum SCL clock frequency in Ultra Fast mode can support maximum bus loading (400pF) when using the high drive pins. The maximum SCL clock frequency for slave in High speed mode can support maximum bus loading (400pF) with appropriate pull-up devices when using the high drive pins. For more information on the required pull-up devices, see I2C Bus Specification.
- 3. See the section "General switching specifications".

5.4.7 Human-machine interfaces (HMI)

5.4.7.1 Touch sensing input (TSI) electrical specifications

Table 67. TSI electrical specificat

Symbol	Description		Value			
		Min	Тур	Мах		
I _{DD_EN}	Power consumption in operation mode	- 500 -		μΑ		
I _{DD_DIS}	Power consumption in disable mode	ition in		nA		
V _{BG}	Internal bandgap reference voltage	_	1.21	_	V	
V _{PRE}	Internal bias voltage	_	1.51	_	V	
Cı	Internal integration capacitance	_	- 90 — p		pF	
F _{CLK}	Internal main clock frequency	_	16	_	MHz	

5.4.8 Debug modules

5.4.8.1 SWD electricals

Table 68. SWD full voltage range electricals

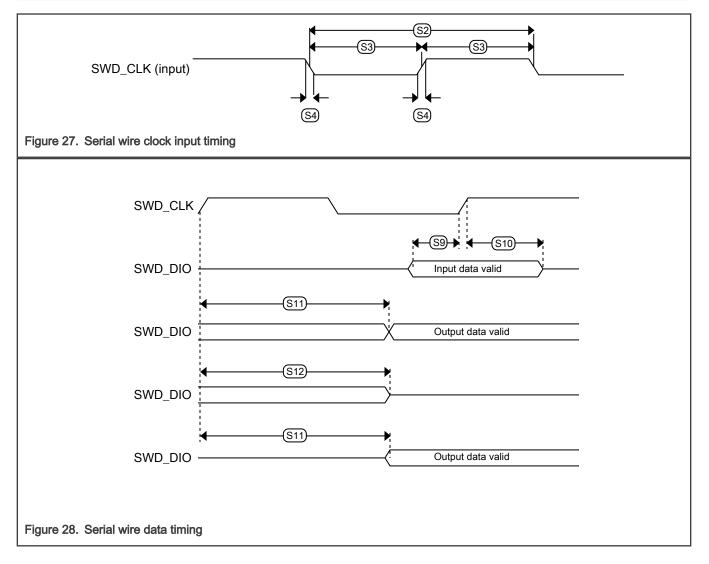
Symbol	Description	Min.	Max.	Unit
V _{DDA}	Operating voltage	2.7	5.5	V
S1	SWD_CLK frequency of operation	0	25	MHz
S2	S2 SWD_CLK cycle period		_	ns

Table continues on the next page ...

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Table 68.	SWD full	voltage range	electricals	(continued)
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S3	SWD_CLK clock pulse width	15	—	ns
S4	SWD_CLK rise and fall times	_	3	ns
S9	SWD_DIO input data setup time to SWD_CLK rise	8	_	ns
S10	SWD_DIO input data hold time after SWD_CLK rise	1.4	_	ns
S11 SWD_CLK high to SWD_DIO data valid		_	25	ns
S12	SWD_CLK high to SWD_DIO high-Z	5	_	ns



6 Design considerations

6.1 Hardware design considerations

This device contains protective circuitry to guard against damage due to high static voltage or electric fields. However, take normal precautions to avoid application of any voltages higher than maximum-rated voltages to this high-impedance circuit.

6.1.1 Printed circuit board recommendations

- Place connectors or cables on one edge of the board and do not place digital circuits between connectors.
- Drivers and filters for I/O functions must be placed as close to the connectors as possible. Connect TVS devices at the connector to a good ground. Connect filter capacitors at the connector to a good ground. Consider to add ferrite bead or inductor to some sensitive lines.
- Physically isolate analog circuits from digital circuits if possible.
- Place input filter capacitors as close to the MCU as possible.
- For best EMC performance, route signals as transmission lines; use a ground plane directly under LQFP packages; and solder the exposed pad (EP) to ground directly under QFN packages.

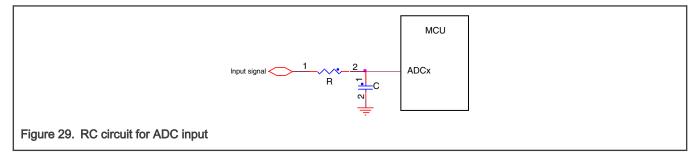
6.1.2 Power delivery system

Consider the following items in the power delivery system:

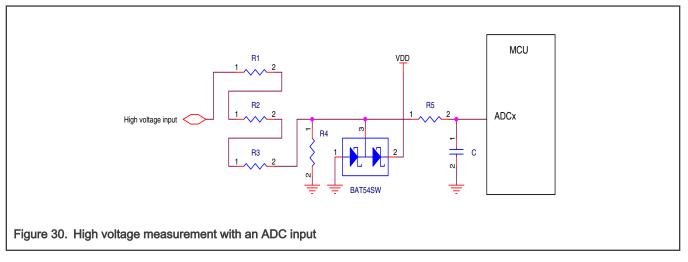
- Use a plane for ground.
- Use a plane for MCU VDD supply if possible.
- · Always route ground first, as a plane or continuous surface, and never as sequential segments.
- · Always route the power net as star topology, and make each power trace loop as minimum as possible.
- · Route power next, as a plane or traces that are parallel to ground traces.
- Place bulk capacitance, 10 μ F or more, at the entrance of the power plane.
- Place bypass capacitors for MCU power domain as close as possible to each VDD/VSS pair, including VDDA/VSSA and VREFH/VREFL.
- The minimum bypass requirement is to place 0.1 µF capacitors positioned as near as possible to the package supply pins.

6.1.3 Analog design

Each ADC input must have an RC filter as shown in the following figure. The maximum value of R must be RAS max if fast sampling and high resolution are required. The value of C must be chosen to ensure that the RC time constant is very small compared to the sample period.



High voltage measurement circuits require voltage division, current limiting, and over-voltage protection as shown the following figure. The voltage divider formed by R1 – R4 must yield a voltage less than or equal to VREFH. The current must be limited to less than the injection current limit. External clamp diodes can be added here to protect against transient over-voltages.



NOTE

For more details of ADC related usage, See AN5250: How to Increase the Analog-to-Digital Converter Accuracy in an Application.

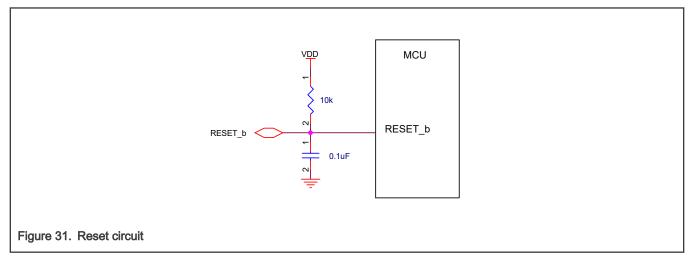
6.1.4 Digital design

Ensure that all I/O pins cannot get pulled above VDD (Max I/O is VDD+0.3V).

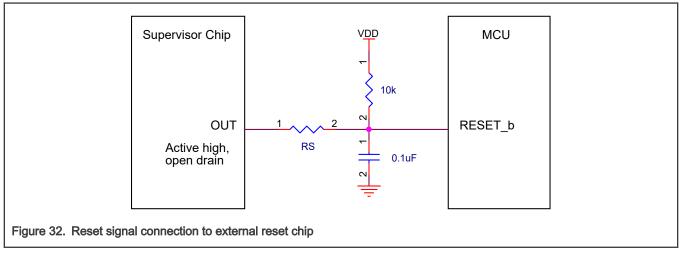
CAUTION: Do not provide power to I/O pins prior to VDD, especially the RESET_b pin.

RESET_b pin

The RESET_b pin is a pseudo open-drain I/O pin that has an internal pullup resistor. An external RC circuit is recommended to filter noise as shown in the following figure. The resistor value must be in the range of 4.7 k Ω to 10 k Ω ; the recommended capacitance value is 0.1 μ F. The RESET_b pin also has a selectable digital filter to reject spurious noise.



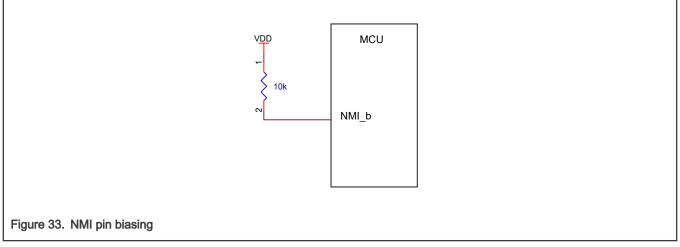
When an external supervisor chip is connected to the RESET_b pin, a series resistor must be used to avoid damaging the supervisor chip or the RESET_b pin, as shown in the following figure. The series resistor value (RS below) must be in the range of 100 Ω to 1 k Ω depending on the external reset chip drive strength. The supervisor chip must have an active high, open-drain output.



NMI pin

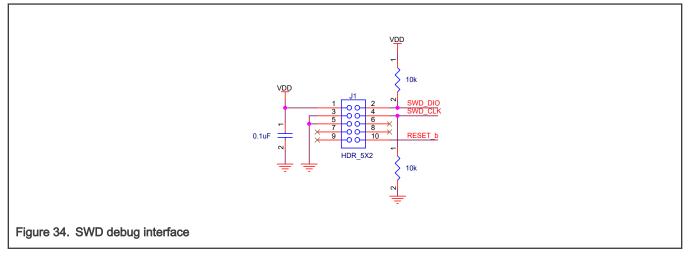
Do not add a pull-down resistor or capacitor on the NMI_b pin, because a low level on this pin will trigger non-maskable interrupt. When this pin is enabled as the NMI function, an external pull-up resistor (10 k Ω) as shown in the following figure is recommended for robustness.

If the NMI_b pin is used as an I/O pin, the non-maskable interrupt handler is required to disable the NMI function by remapping to another function. The NMI function is disabled by programming the FOPT[NMI_DIS] bit to zero.



• Debug interface

This MCU uses the standard ARM SWD interface protocol as shown in the following figure. While pull-up or pull-down resistors are not required (SWD_DIO has an internal pull-up and SWD_CLK has an internal pull-down), external 10 k Ω pull resistors are recommended for system robustness. The RESET_b pin recommendations mentioned above must also be considered.



Unused pin

Unused GPIO pins must be left floating (no electrical connections) with the MUX field of the pin's PORTx_PCRn register equal to 0:0:0. This disables the digital input path to the MCU.

6.1.5 Crystal oscillator

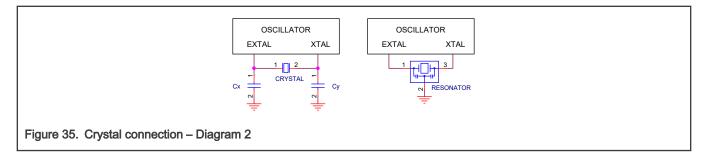
When using an external crystal or ceramic resonator as the frequency reference for the MCU clock system, refer to the following table and diagrams.

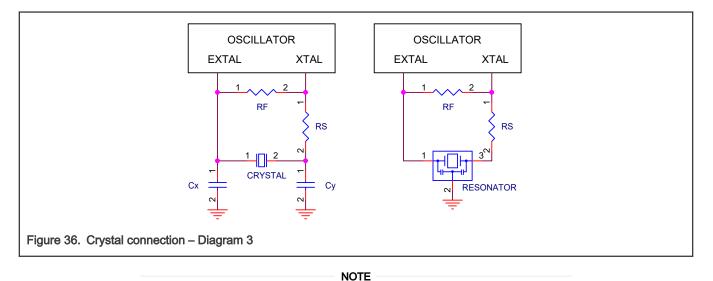
The feedback resistor, RF, is incorporated internally with the low power oscillators. An external feedback is required when using high gain (HGO=1) mode.

The series resistor, RS, is required in high gain (HGO=1) mode when the crystal or resonator frequency is below 2 MHz. Otherwise, the low power oscillator (HGO=0) must not have any series resistance; and the high frequency, high gain oscillator with a frequency above 2 MHz does not require any series resistance.

Table 69. External crystal/resonator connections

Oscillator mode	Oscillator mode
Low frequency (32.768 kHz), high gain	Diagram 3
High frequency (1-32 MHz), low power	Diagram 2
High frequency (1-32 MHz), high gain	Diagram 3





For PCB layout, the user could consider to add the guard ring to the crystal oscillator circuit.

7 Revision history

Table 70 provides a revision history for this document.

Table 70. Revision history

Rev. No.	Date	Substantial Changes
Rev. 2	04/2024	Added HSRUN mode in Kinetis KE17Z/13Z/12Z introduction
		Updated Ordering information
		Updated Figure 2
		Updated Memory
		Updated Table 7
		Added TSI
		Updated ESD handling ratings
		UPdated descritions of Power consumption
		Updated Low power mode peripheral current adder — typical value
Rev. 1	11/2023	Initial version

Legal information

Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions"

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <u>https://www.nxp.com</u>.

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